

MAINTENANCE MANUAL 406-512 MHz, 100 WATT POWER AMPLIFIER ASSEMBLY 19D424888G14-17, G31-34, G37 AND G38 (MOBILE AND STATION) 19D424895G14-17, G31-34, G38, G39, AND G40-43 (CONTINUOUS DUTY STATION)

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DESCRIPTION

The PA assembly uses two amplifier modules to provide rated output power. The PA Driver module uses four RF power transistors to provide RF drive to the PA module. The Power Amplifier module conmodule. sists of four paralleled RF Power Transistors connected by a transmission line splitter arrangement at the input, and a combiner arrangement at the output. R213, located on the PA Driver module, is used to adjust the output power over a range of 30 Watts to rated output power. The power control circuit consists of R213, Q215 and Power Control IC (U201). Included in the PA assembly, is a Low Pass Filter/Antenna Switch module used to suppress undesired harmonic frequency components and provide antenna switching for the receiver and the transmitter.

SUPPLY VOLTAGE

Supply voltage for the PA is connected through power leads from the system board to feed through capacitors C297 and C298 on the bottom of the PA assembly (See Schematic Diagram). C297, C298, C299 prevent RF from getting on the power leads. Diodes CR295 will cause the main fuse assembly to blow if the polarity of the power leads is reversed, providing reverse voltage protection for the radio.

The PA assembly is insulated from vehicle ground to permit operation in positive or negative ground vehicles.

- NOTE -

In positive ground vehicles, A"hot" with respect to vehicle
ground. Shorting the transmitter
PA printed wiring board ground
pattern to the radio case may
cause one of the in-line fuses to
blow.

Centralized metering jack J205 is provided for use with GE Test Set Model 4EX3A11 or Test Kit 4EX8K12. The Test Set meters the Ampl-1 drive (exciter output), power control voltage, driver current, PA current and PA voltage.

CIRCUIT ANALYSIS

RF POWER AMPLIFIER ASSEMBLY

The exciter output is coupled through at 50 ohm RF cable to the PA Drive module input jack J201. The 50 ohm RF input is coupled through a matching network comprised of C207, C208 and W202 to the base of power amplifier Q201.

Part of the RF input is rectified by CR201 and metered at J205-4 through resistor R201. The rectified RF is also applied to the power control IC (U201).

Collector voltage for Q201 is applied direct from the DC power input through collector stabilizing network R205 and L202 and collector feed network L203 and C210.

The 500 milliwatt, 50 ohm output of Q201 is coupled to the base of a second power amplifier Q202 through a matching network consisting of T201, C214, C215, C216 and L204.

Collector voltage to Q202 is controlled by power control IC (U201), Q215 and R213, and is applied through a collector stabilizing network L206 and R206 and collector feed network L205 and C218.

The 6 Watt, 50 ohm output of Q202 is coupled to the base of Q203 through C219 and the matching network of T202, C222, C224, C225 and L207. The collector voltage to Q203 is coupled through collector stabilizing network L209 and R214 and collector feed network L208 and C228.

The 20-Watt output of Q203 is coupled through an impedance matching network (C229, C230, C233 and T203) that matches the output impedance of Q203 to the input impedance of driver amplifier Q204 through a 50-ohm micro strip (W204) and input impedance matching network T204, C234, C235 and C236.

The collector voltage for Q204 is coupled through collector stabilizing network L212 and R208 and collector feed network C239 and L211. Collector current for Q204 is metered across tapped manganin resistor R212. The reading taken in position F on the 15-Volt scale with the High Sensitivity button pressed and read as 0-15 amperes full scale.

Following Driver amplifier Q204 is 50-ohm a matching network (C237, C238, and T205) that matches the 40 Watt output of Q204 to the 50-ohm input of the PA module, through 50-ohm micro strip W207 and a 50-ohm strap W211.

— NOTE —

For MASTR® II High Power Solid State applications where "Combining" is used, four new Power Amplifiers (19D424895G40-G43) have been added. The new PA's do not use the 40 Watt modules. Two separate PA's are used with a combiner panel to sum the power output of each PA.

On the PA module, the RF input is applied to the RF power splitter board. The RF power splitter consisting of micro strip transmission line W4201, C4265, C4266, R4201, R4202 and R4203, and has a 50-ohm input and output impedance. The outputs of the power splitter are applied to the four identical Class C Power Amplifiers (Q216 through Q219) via their respective identical matching networks.

Supply voltage for Q216 through Q219 is coupled through identical stabilizing networks and the collector feed networks. Supply voltage is measured in position G on the 15-volt range with the polarity switch in the (-) position (read as 15 volts full scale).

Collector current for Q216 through Q219 is metered across paralleled tapped manganin resistors R210 and R211 located on the PA Driver module. The reading is taken in Position G in the Test 1 position on the 3-Volt scale with the "High" Sensitivity Button pressed, and read as 30 amperes full scale.

The outputs of Q216 through Q219 are coupled through identical matching networks to the RF power combiner board. The RF power combiner consists of micro strip transmission line W4202, R4208, R4209, and R4210, and has a 50-ohm input and output impedance. The combiner adds the outputs of Q216 through Q219, and applies the combined RF output to the Low Pass Filter/Antenna Switch module via W4216. Capacitors C4243 through C4252 provide isolation for + ground operation.

The input to the Low Pass Filter and to the antenna switch K201 is coupled through the 50-ohm micro strip W4280. The output is applied to the antenna at J203.

--- WARNING -

The RF Power Transistors used in the transmitter contain Beryllium Oxide, a TOXIC substance. If the ceramic, or other encapsulation is opened, crushed, broken or abraded, the dust may be hazardous if inhaled. Use car in placing transistors of this type.

POWER CONTROL CIRCUIT

The Power Control Circuit, located on the PA Driver module, consists of CR201, Power Control IC (U201), RT201, Q215, and R213.

When the transmitter is keyed, rectified RF from CR201 is applied to Switch Q1 of Power Control IC (U201), turning it on (See Figure 1). Turning on Q1 turns on voltage regulator Q2, supplying a constant voltage via Pin 14 to Power Adjust potentiometer R213. R213 through Pin 12 connect to the base of Q5. Q5, Q6 and Q215 operate as an amplifier chain to supply voltage to the collector of Q202 (Ampl-2). The setting of R213 determines the voltage applied to the base of Q5. The higher the voltage at the base of Q5, the harder the amplifiers conduct, supplying more

collector voltage to Q202. The lower the voltage at the base of Q5, the less collector voltage is supplied to Q202. Reducing the supply voltage to Q202 reduces the drive to Q203 and Q204, thereby reducing the power output of the PA. The power output can be adjusted by R213 from 30 Watts to rated power output.

Temperature protection is provided by Q4 in IC U201 and thermistor RT201 which is mounted on the PA heatsink. Under normal operating conditions, the circuit is inactive (Q3 is on and Q4 is off). When the heatsink temperature reaches approximately 115°C the resistance of RT201 decreases. This increases the base voltage applied to Q3, turning it off. Turning off Q3 allows Q4 to turn on, decreasing the voltage at Power Adjust potentiometer R213. This reduces the base voltage to Q5 which causes Q6 and Q215 to conduct less, reducing the collector voltage to Q202 This reduces the transmitter (Ampl-2). output power, keeping the heatsink at a maximum of approximately 115°C. When the heatsink temperature decreases below 115°C, the temperature control circuit turns off,

allowing the normal transmitter power output.

ANTENNA MATCHING UNIT

The Antenna Matching Unit is used only in continuous duty duplex stations to optimize impedance matching between the power amplifier and the load. It consists of a Pi network (C2-C5 and L1) and a reverse directional coupler. RF from the low pass filter is applied to the Pi network through the reverse directional coupler and then to the duplexer load. The reverse directional coupler permits monitoring the reflected power by connecting a DC voltmeter across TP1 (+) and ground (-). C2 and C4 are tuned for minimum DC voltage which represents minimum reflected Power. L1 may also be pushed toward or away from the filter cover wall to further reduce the DC voltage. C2, C4 and L1 should be alternately tuned until an absolute minimum voltage reading is obtained. The residual voltage reading after tuning may vary from one transmitter to the next depending on output power level, operating frequency and the load.

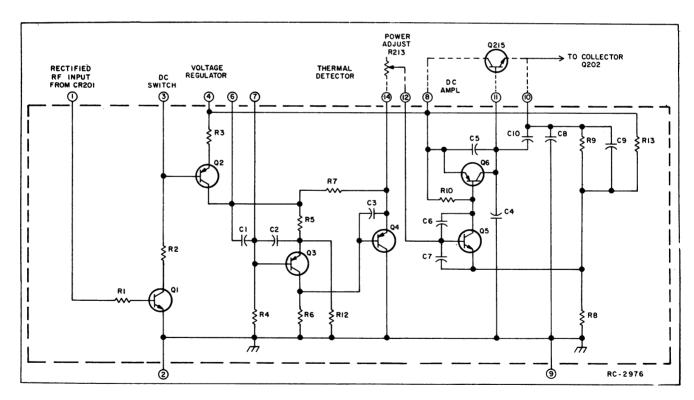


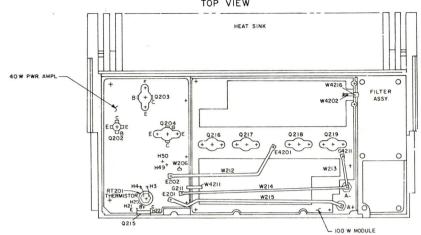
Figure 1 - Power Control IC-U201

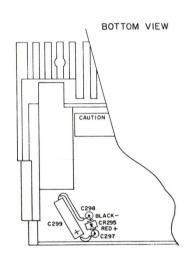


L

GE Mobile Communications

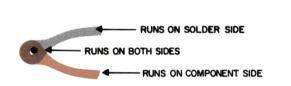
PA ASSEMBLY TOP VIEW

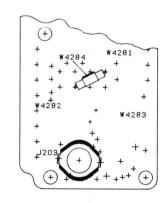




(19D424161, Rev. 5)

DUPLEX STATION FILTER BOARD



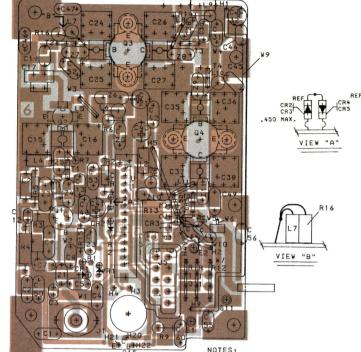


OUTLINE DIAGRAMS

100 WATT UHF MOBILE AND INTERMITTENT DUTY STATION POWER AMPLIFIER

40 WATT MODULE

TOP



(19C327332, Rev. 14) (19B226633, Sh. 1, Rev. 6) (19B226633, Sh. 2, Rev. 3)

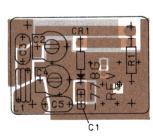
MOBILE & STATION

(19C327643, Rev. 1) (19B227265, Sh. 1, Rev. 1) (19B227265, Sh. 2, Rev. 1)

FILTER BOARD

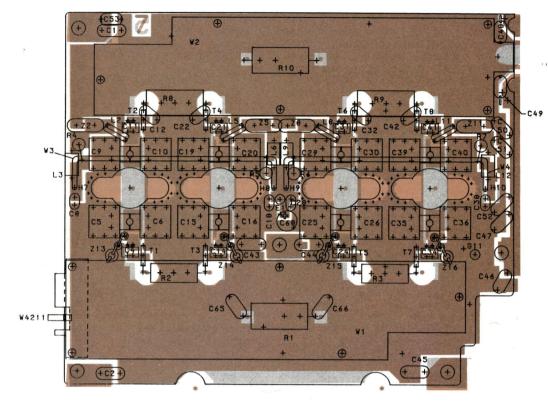
NOTES:
1. PARTIAL REFERENCE DESIGNATIONS
ARE SHOWN.FOR COMPLETE
DESIGNATION, PREFIX WITH 200
SERIES.EXAMPLE:
C1-C201, R1-R201, ETC.
2. C9 USED IN GROUP 5 ONLY. DA
JUMPER IN C9 MTG HOLESFOR
GROUP 6,.7 & 8.
3. Q2.Q3 AND Q4 ARE PART OF HIGHER
ASM (PA).

ANTENNA MATCHING



(19B233800, Rev. 0) (19A143200, Sh. 1, Rev. 0) (19A143200, Sh. 2, Rev. 0)

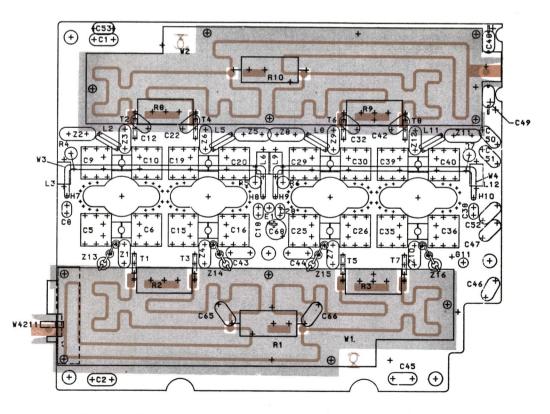
100 WATT MODULE



(19C327331, Rev. 12) (19B226639, Sh. 1, Rev. 7) (19B226639, Sh. 2, Rev. 5)

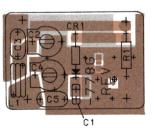
NOTE:

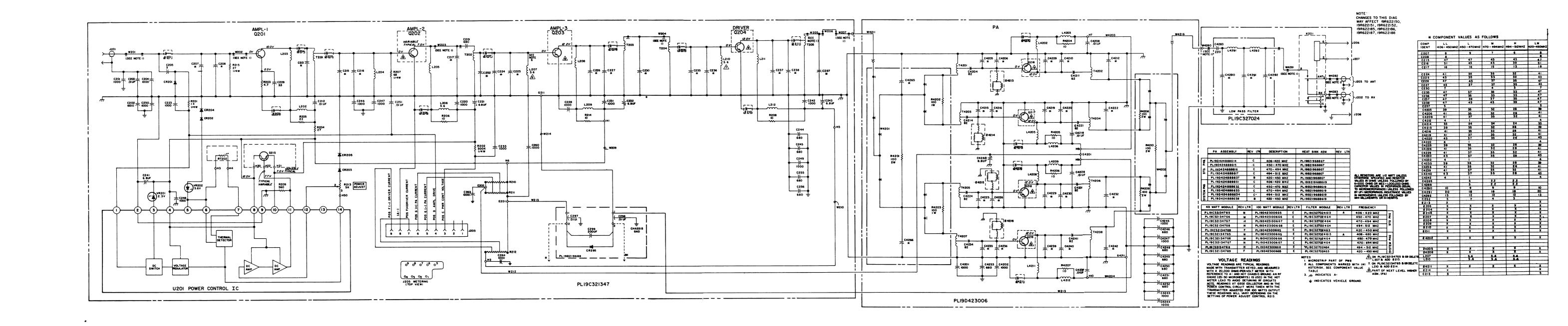
1. PARTIAL REFERENCE DESIGNATIONS ARE SHOWN,
FOR COMPLETE DESIGNATIONS PREFIX WITH
4200 SERIES. EXAMPLE:C15-C4215,R1-R4201,
ETC.



(19C327331, Rev. 11) (19B226642, Sh. 1, Rev. 3) (19B226642, Sh. 2, Rev. 3)

UNIT





SCHEMATIC DIAGRAM

100 WATT UHF MOBILE & INTERMITTENT DUTY STATION POWER AMPLIFIER

Issue 10

PARTS LIST

LBI30203J

SYMBOL

C207M*

C207H

C208LL

C208L*

C208M*

C208H*

C209LL*

C209L*

C209M*

C209H*

C209*

C210LL*

C210L*

C210M*

C210H*

C211LL*

C211L*

C211M*

C211H*

C212

C213*

C213LL*

C214L*

C214M*

C214H*

C215LL

C215L

C215M

C215H

C216LL

C216L

C216M

C216H

GE PART NO.

19A116656P7J0

19A116656P6J

19A116656P6J

19A116656P8J0

19A116656P6J

19A116656P6J

7489162P15

7489162P11

7489162P11

19A116656P33

19A134666P3

19A134666P1

19A134666P1

19A134666P

19A134666P

19A134666P

19A134666P1

19A116192P1

19A116656P5J0

19A134666P1

19A134666P1

19A700131P47

19A700131P47

19A700131P43

19A700131P51

19A700131P43

194700131P43

19A700131P39

C214LL* 19A134666P3

In REV E & earlier:

Deleted in G9 by REV D.

Metallized teflon: 43 pF +2%, 250 VDCW.

Metallized teflon: 39 pF ±2%, 250 VDCW.

406-512 MHz, 100 WATT POWER AMPLIFIER
19D424888G14-G17, ("M" SERIES MOBILE, INT. DUTY STATION) - REV C
19D42488BG37, ("M" SERIES MOBILE, INT. DUTY STATION) - REV B
19D42488BG31-G34, ("E" SERIES MOBILE) - REV C SYMBOL GE PART NO DESCRIPTION - - - - - - - TRANSISTORS - - - - -Silicon, NPN: sim to Type 2N5945. 19A134164P2 Q203LL 9A134239P3 Silicon, NPN. Q203L Silicon, NPN. A134239P1 Q203M A 134239P1 Silicon, NPN. Q203H Silicon, NPN Q204LL and Q204L Silicon, NPN. 9A134242P3 Q204H 9A134242P4 Silicon, NPN; 50 Watt. Q215 19A116742P1 Silicon, NPN. Silicon, NPN; sim to Type 2N5945 - - - - - - - THERMISTORS - - - - - -19A129379G1 Thermistor: 40K ohms $\pm 20\%$, color code white; si RT201 o Carborundum Type M0806J-5. - - - - - - - - - CABLES - - - - - - -9A130486G1 W213 B227092G1 B226725G1 W215 19B227074G1 W4216 A130479P3 40 WATT MODULE 19C321347G5 406-420 MHz (LL) 19C321347G6 450-470 MHz (L) 19C321347G7 470-494 MHz (M) 19C321347G8 494-512 MHz (19C321347G9 420-450 MHz - - - - - - - - CAPACITORS - - - - - -Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap. A116655P20 C203 9A116192P1 eramic: 0.01 uF +20%, 50 VDCW; sim to Erie 8121 C204 eramic disc: 1000 pF \pm 10%, 1000 VDCW; sim to C205 A 116656P3.J Ceramic disc: 3 pF +0.5 pF, 500 VDCW, temp coe Silver mica: 18 pF +5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted in G5 by REV L. Deleted in G6 by REV K. Deleted in G7 & G8 by C206* A134666P1 REV H. Deleted in G9 by REV D. In REV E & earlier in G5, in REV C & earlier in Ceramic disc: 680 pF \pm 10%, 1000 VDCW; sim to RMC Type JF Discap. 19A116655P18 C207LL Ceramic disc: 8 pF +0.5 pF, 500 VDCW; temp coef 19A116656P8J0 19A116656P9J Ceramic disc: 9 pF ±0.5 pF, 500 VDCW, temp coe 0 PPM. In REV D & earlier: Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.

DESCRIPTION SYMBOL | GE PART NO DESCRIPTION eramic disc: 7 pF ±0.5 pF, 500 VDCW, temp coef C217LL 19A116679P18E Metallized teflon: 18 pF +0.5 pF. 250 VDCW. C217L 19A116679P16D Metallized teflon: 16 pF +0.5 pF, 250 VDCW. Ceramic disc: 6 pF \pm 0.5 pF, 500 VDCW, temp coef 0 PPM. C217M 19A116679P15D Metallized teflon: 15 pF ±0.5 pF, 250 VDCW. C217H 19A116679P13D Metallized teflon: 13 pF +0.5 pF, 250 VDCW. Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef Silver mica: 18 pF ±5%, 500 VDCW; sim to Electr Motive Type DM154CR. Deleted in G5 by REV L. Deleted in G6 by REV K. Deleted in G7 & G8 by REV H. Deleted in G9 by REV D. C218* 19A134666P1 Ceramic disc: 8 pF ±0.5 pF, 500 VDCW; temp coef Ceramic disc: 680 pF \pm 10%, 1000 VDCW; sim to RM Type JF Discap. C219 19A116655P18 Ceramic disc: 6 pF ± 0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV E. C220 19A116655P20 Ceramic disc: 1000 pF \pm 10%, 1000 VDCW; sim to Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV F. C221 19B209723P4 Tantalum: 6.8 uF +20%, 35 VDCW. Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV F. C222LL* 19A134666P3 Silver mica: 27 nF +5% 500 VDCW: sim to Electr Silver mica: 33 pF $\pm 5\%$, 500 VDCW; sim to Electro Motive Type DM-15. Deleted by REV C. Added by REV D. Deleted by REV G. C222L* 19A134666P1 Silver mica: 18 pF +5%, 500 VDCW; sim to Elect Motive Type DM154CR. Deleted in G6 by REV K. Silver mica: 22 pF ±5%, 500 VDCW; sim to Electro Motive Type DM-15. Deleted by REV C. Silver mica: 18 pF $\pm 5\%$, 500 VDCW; sim to Elect Motive Type DM154CR. Deleted in G7 by REV H. Silver mica: 22 pF ±5%, 500 VDCW; sim to Electr Motive Type DM-15. Deleted by REV C. Silver mica: 18 pF ±5%, 500 VDCW; sim to Elect Motive Type DM154CR. Deleted in G7 by REV H. C222H* 19A134666P1 Silver mica: 27 pF +5%, 500 VDCW; sim to Electr Motive Type DM-15. Deleted by REV C. Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap. C223 19A116655P20 Ceramic disc: 33 pF ±5%, 500 VDCW, temp coef 0 PPM. Added to G5 by REV G, G6 by REV E, G7 & G8 by REV F. C224LL 19A700131P4 Metallized teflon: 41 pF +2%, 250 VDCW. C224L 19A700131P35 Metallized teflon: 35 pF +2%, 250 VDCW. Motive Type DM154CR. Deleted in G5 by REV L. C224M 19A700131P35 Metallized teflon: 35 pF +2%, 250 VDCW 19A700131P32 Metallized teflon: 32 pF ±2%, 250 VDCW. C224H Silver mica: 18 pF \pm 5%, 500 VDCW; sim to Elec Motive Type DM154CR. Deleted in G6 by REV K. Metallized teflon: 43 pF ±2%, 250 VDCW. C225LL 19A700131P43 Silver mica: 18 pF +5%, 500 VDCW; sim to Electro C225L 19A700131P35 Metallized teflon: 35 pF +2%, 250 VDCW. Motive Type DM154CR. Deleted in G7 by REV H. C225M 19A700131P33 Metallized teflon: 33 pF +2%, 250 VDCW. Notive Type DM154CR. Deleted in G8 by REV H. Metallized teflon: 32 pF +2%, 250 VDCW. C225H 19A700131P32 Silver mica: 27 pF \pm 5%, 500 VDCW; sim to Electromotive Type DM154CR. Deleted in G5 by REV L. Deleted in G9 by REV D. Metallized teflon: 47 pF +2%, 250 VDCW C226LL Metallized teflon: 43 pF ±2%, 250 VDCW. C226L 19A700131P43 Silver mica: 18 pF +5%, 500 VDCW; sim to Electro C226M 19A700131P3 Metallized teflon: 37 pF ±2%, 250 VDCW. Notive Type DM154CR. Deleted in G6 by REV K. C226H 19A700131P35 Metallized teflon: 35 pF ±2%, 250 VDCW. Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted in G7 by REV H. C227LL 19A700131P43 Metallized teflon: 43 pF +2%, 250 VDCW Silver mica: 18 pF +5%, 500 VDCW; sim to Elect C227L 19A700131P37 C227M 19A700131P3 Metallized teflon: 37 pF +2%, 250 VDCW. Ceramic: 0.01 uF +20%, 50 VDCW; sim to Erie 8121 C227H 19A700131P35 Metallized teflon: 35 pF ±2%, 250 VDCW. Ceramic disc: 4 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV E. C228 19A116655P20 Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to MC Type JF Discap. Ceramic disc: 5 pF ± 0.5 pF, 500 VDCW, temp coef 0 PPM. Added by REV E. Deleted in G5 by REV M. Deleted in G9 by REV E. Added to G5 by REV N. Added to G9 by REV F. C229LL* 19A134666P3 Silver mica: 27 pF +5%, 500 VDCW; sim to Electi Motive Type DM154CR. Deleted in G5 by REV L. Deleted in G9 by REV D. C229L* 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electr Motive Type DM154CR. Deleted in G6 by REV K. Silver mica: 27 pF +5%, 500 VDCW; sim to Electro Silver mica: 18 pF +5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted in G7 by REV H. C229M* 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electronotive Type DM154CR. Deleted in G6 by REV K. Silver mica: 18 pF \pm 5%, 500 VDCW; sim to Electr Motive Type DM154CR. Deleted in G8 by REV H. 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electr Motive Type DM154CR. Deleted in G7 by REV H. 19A116656P7J0 Ceramic disc: 7 pF ±0.5 pF, 500 VDCW, temp coef Silver mica: 18 pF +5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted in G8 by REV H. In G5 of REV K & earlier: In G9 of REV C & earlier: Metallized teflon: 47 pF ±2%, 250 VDCW. 19A116656P8J0 Ceramic disc: 8 pF ±0.5 pF, 500 VDCW; temp coef Metallized teflon: 47 pF +2%, 250 VDCW. Metallized teflon: 43 pF ±2%, 250 VDCW. 19A116656P4J0 Ceramic disc: 4 pF ±0.5 pF, 500 VDCW, temp coef C230M Metallized teflon: 43 pF +2%, 250 VDCW 9A116656P3 eramic disc: 3 pF ±0.5 pF, 500 VDCW, temp coef Metallized teflon: 51 pF +2%, 250 VDCW Metallized teflon: 43 pF +2%, 250 VDCW. C231 9A116655P20 Ceramic disc: 1000 pF +10%, 1000 VDCW; sim to

C232

C233L*

19B209723P4

9A134100P20

Tantalum: 6.8 uF ±20%, 35 VDCW.

SYMBOL GE PART NO. DESCRIPTION C233H* 19A134100P20 Ceramic disc: 2.2 pF ±0.1 pF, temp coef 0 ±120 PPM. Deleted by REV B. Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted in G5 by REV L. C234LL* 19A134666P3 Deleted in G9 by REV D. Silver mica: 18 pF \pm 5%, 500 VDCW; sim to Elect Motive Type DM154CR. Deleted in G6 by REV K. C234L* 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electr Motive Type DM154CR. Deleted in G7 by REV H. C234M* 19A134666P1 Silver mica: 18 pF \pm 5%, 500 VDCW; sim to Electr Motive Type DM154CR. Deleted in G8 by REV H. C234H* 19A134666P1 Metallized teflon: 47 pF +2%, 250 VDCW. 19A700131P47 In G5 of REV K & earlier: In G9 of REV C & earlier: Metallized teflon: 43 pF ±2%, 250 VDCW. Metallized teflon: 37 pF +2%, 250 VDCW. C235L 19A700131P37 C235M 19A700131P35 Metallized teflon: 35 pF ±2%, 250 VDCW. C235H 19A700131P33 Metallized teflon: 33 pF +2%, 250 VDCW. C236LL* 19A700131P47 Metallized teflon: 47 pF +2%, 250 VDCW. 194116952030 Metallized teflon: 39 pF +2%, 250 VDCW. Metallized teflon: 35 pF +2%, 250 VDCW. C236L C236M 19A700131P33 Metallized teflon: 33 pF +2%, 250 VDCW. C236H Metallized teflon: 33 pF +2%, 250 VDCW. C237LL 19A700131P47 Metallized teflon: 47 pF ±2%, 250 VDCW. C237L 19A700131P39 Metallized teflon: 39 pF +2%, 250 VDCW. C237M Metallized teflon: 37 pF ±2%, 250 VDCW. 19A700131P37 C237H* 19A700131P35 Metallized teflon: 35 pF +2%, 250 VDCW. In REV D & earlier: Metallized teflon: 33 pF +2%, 250 VDCW. 19A116952P33 C238LL 19A700131P47 Metallized teflon: 47 pF +2%, 250 VDCW. C238L Metallized teflon: 43 pF ±2%, 250 VDCW. C238M* 19A700131P43 Metallized teflon: 43 pF ±2%, 250 VDCW. In REV D & earlier: Metallized teflon: 37 pF ±2%, 250 VDCW. 19A116952P37 C238H* 19A700131P39 Metallized teflon: 39 pF +2%, 250 VDCW. In REV D & earlier: Metallized teflon: 33 pF +2%, 250 VDCW 19A116952P33 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted in G5 by REV H. Deleted in G6 by REV K. Deleted in G7 & G8 by C239* 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM-15. Added by REV H. Deleted in C239LL* 7489162P13 G5 by REV L. G9 by REV D. Silver mica: 27 pF \pm 5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted in G5 by REV L. Deleted in G9 by REV D. C240LL* 19A134666P3 C240L* 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted in G6 by REV K. Silver mica: 18 pF +5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted in G7 by REV H. C240M* 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electr Motive Type DM154CR. Deleted in G8 by REV H. C240H* 19A134666P1 C241 19A134202P15 Tantalum: 6.8 uF +20%, 35 VDCW. C242 Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap. Tantalum: 6.8 uF +20%, 35 VDCW. C243 19A134202P1 Ceramic disc: 680 pF $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap. C246 thru C250 Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap. 9A116655P20 Ceramic disc: 2.2 pF ±0.1 pF, temp coef 0 ±120 PPM. Deleted by REV B.

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL
C251	19A116192P1	Ceramic: 0.01 uF ±20%, 50 VDCW; sim to Erie 8121 Special.	
C252LL*	19A116656P5J0	Ceramic disc: 5 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L202
		In G5 of REV H-M:	L203
İ	19A116656P9J0	Ceramic disc: 9 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L204
		In REV B-G:	L205 L206
	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L207*
	19A116656P4J0	In REV A & earlier: Ceramic disc: 4 pF ±0.5 pF, 500 VDCW, temp coef	L208LL
	1941100307430	O PPM.	L208L L208M
C252L*	19A116656P7J0	Ceramic disc: 7 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L208H
		In REV C-H:	L209
	19A116656P5J0	Ceramic disc: 5 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Added by REV B.	L210LL*
C252M*	19A116656P4J0	Ceramic disc: 4 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Added by REV B.	L210L
C252H*	19A116656P3J0	Ceramic disc: 3 pF +0.5 pF, 500 VDCW, temp coef	L210M
C253	19A116655P20	O PPM. Added by REV B. Ceramic disc: 1000 pF +10%, 1000 VDCW; sim to	L210H
Ì		RMC Type JF Discap.	L211 L212
C255 and C256	19A116655P18	Ceramic disc: 680 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	
C257LL*	19A116656P5J0	Ceramic disc: 5 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	Q201
		In G5 of REV M: In G9 of REV E:	
	19A116656P7J0	Ceramic disc: 7 pF ±0.5 pF, 500 VDCW, temp coef	R201
		O PPM. In G5 of REV L & earlier:	R202 R203*
	19A116656P5J0	In G9 of REV D & earlier: Ceramic disc: 5 pF ±0.5 pF, 500 VDCW, temp coef	R203*
00521.		0 PPM.	R204*
C257L*	19A134100P20	Ceramic disc: 2.2 pF ±0.1 pF, temp coef 0 ±120 PPM. Deleted by REV B.	
C257M*	19A134100P19	Ceramic disc: 1 pF ±0.1 pF, temp coef 0 ±250 PPM. Deleted by REV B.	R205
C257H*	19A134100P19	Ceramic disc: 1 pF ±0.1 pF, temp coef 0 ±250 PPM. Deleted by REV B.	R206
C258L*	19A116656P3J0	Ceramic disc: 3 pF +0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV C.	R207 R208
C260	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R209
C262*	19A116114P2044	Ceramic: 27 pF +5%, 100 VDCW; temp coef -80 PPM. Added to G6 by REV F. Deleted from G6 by REV G.	R210 thru R212
C263*	19A116655P20	Ceramic disc: 1000 pF +10%, 1000 VDCW; sim to	R213
and C264*		RMC Type JF Discap. Added to G5 by REV K. Added to G6 by REV H. Added to G7, G8 by REV G. Added to G9 by REV C.	
		DIODES AND RECTIFIERS	R214
CR201	19A116052P1	Silicon, hot carrier: Fwd drop .350 volts max.	R215 R216*
CR202 and CR203	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.	R216*
CR204* and CR205*	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV. Added by REV A.	T201 thru
CREOO			T205
E201 and E202	19A134263P1	Contact, electrical: sim to Selectro 229-1082-00-0-590.	U201
G211	19A134263P1	Contact, electrical: sim to Selectro 229-1082-00-0-590.	VR201
		JACKS AND RECEPTACLES	VR202
J201	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim to NTTF-1058.	
J205	19B219374G1	Connector: 9 contacts.	

, ,	SYMBOL	GE PART NO.	DESCRIPTION
	W201 thru W205		(Part of printed board 19D423005P1).
	W206	19A701093P1	Strap.
	W207		(Part of printed board 19D423005P1).
o Jeffers 4422-1K.	W209	19B226733G1	Jumper.
o Jeffers 4421-4K. REV E.	W2 10	19B226734G1	Jumper. FREQUENCY SELECTING NETWORKS
1 }	Z201*	19A134666P1	Frequency network: selective, 470-630 MHz res.
	2201	13813400071	freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G5 by REV L. Added to G6 by REV K. Added to G7 & G8 by REV H. Added to G9 by REV D.
Jeffers 4421-9K.	Z203LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.
REV E. o Jeffers 4421-4K.	Z203L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.
o Jeffers 4421-4K.	Z203M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
	Z203H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.
RS	Z204LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.
1 w.	Z204L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.
/4 w. 2 w. Deleted by	Z204M*	19A134666P!	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
to G6 by REV E, to	Z204H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.
w.	Z205LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.
w. w.	Z205L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.
w.	Z205M*	19A134666Pi	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
2 ₩•	Z205H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:MP0:240J:SLAC. Added to G8 by REV H.
20%, 1/2 w; sim to	Z206*	19A134666P1	Prequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G5 by REV L. Added to G9 by REV D. Added to G6 by REV K. Added to G7 & G8 by REV H.
2 w.	Z207LL*	19A134666P3	Frequency network: selective, 400-500 MHz res.
4 w. 2 w. Added to G6 by			freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.
s	Z207L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.
	Z207M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
RCUITS	Z207H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.
	Z208LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.
TORS			

DESCRIPTION

- - - - - - - INDUCTORS

oil, RF: 5.6 uH +10%; sim

Coil, RF: 5.6 uH ±10%; sim to Deleted in G5 by REV M, G9 by

Coil, RF: 15 uH +10%; sim t Deleted in G5 by REV M, G9 b

Coil. RF: 5.6 uH +10%; sim

Coil, RF: 5.6 uH +10%; sim

oil RF: 5.6 uH +10%: sim

- - - - - - TRANSIST

- - - - - - - RESISTOR

Composition: 1K ohms ±5%,

Composition: 300K ohms ±5%,

Composition: 4.7 ohms ±5%, REV C. Added by REV D. Add

omposition: 27 ohms ±5%,

Composition: 22 ohms ±5%,

Composition: 22 ohms ±5%,

omposition: 10 ohms +5%,

Composition: 68 ohms ±5%,

Composition: 10 ohms ±5%,

composition: 560 ohms ±5%,

ariable cermet: 5000 ohms

Composition: 10 ohms ±5%,

Composition: 27 ohms ±5%,

Composition: 10 ohms ±5%,

- - - - - - - TRANSFORM

- - - - - - INTEGRATED

- - - - - - VOLTAGE REG

Zener: 500 mW, 2.3 v. nomin

Zener: 500 mW. 5.4 v. nomi

G7 & G8 by REV F.

Shunt resistor.

TS Series 360.

Power Control.

In REV B & earlier:

Silicon, NPN.

GE PART NO

19A701091G1

19A129774P1

19A701091G1

19B219457P6

19A700000P120

19B219457P6

19A130650P1

19A130650P1

19A130650P1

19A701091G1

19A700000P25

9A700000P20

19A700000P20

19470000020

19B219457P6

19A701091G1

19A134237P1

19A700106P63

3R152P304J

19A700113P7

19A700113P25

3R77P220J

19A700106P23

19A700113P15

19A700106P35

19A700113P15

19A700113P57

19C850605P1

19A116559P102

19A700113P15

19A700106P25

19A700113P15

19A130446G1

19D423127G1

4036887P1

4036887P5

SYMBOL	GE PART NO.	DESCRIPTION
Z208M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to 67 by REV H.
Z208H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.
Z209LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.
Z209L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.
Z209M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
Z209H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.
Z210*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G5 by REV L. Added to G9 by REV D. Added to G6 by REV K.
Z211LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.
Z211L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.
Z211M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
Z211H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.
Z213* and Z214*	19A143581G1	Network assembly. Added to G5 by REV M. Added to G9 by REV E.
		100 WATT MODULE 19D423006G5 406-450 MHz (LL) 19D423006G6 450-470 MHz (L) 19D423006G7 470-494 MHz (M) 19D423006G8 494-512 MHz (H) (REV E)
C4201 and C4202	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.
C4204LL*	19A134666P3	Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C.
C4204L*	19A134666P1	Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C.
C4. 04M*	19A134666P1	Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C.
C4204H*	19A134666P1	Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C.
C4205LL	19A700131P39	Metallized teflon: 39 pF ±2%, 250 VDCW.
C4205L	19A700131P35	Metallized teflon: 35 pF ±2%, 250 VDCW.
C4205M C4205H	19A700131P32	Metallized teflon: 32 pF ±2%, 250 VDCW.
C4205H	19A700131P28 19A700131P41	Metallized teflon: 28 pF ±2%, 250 VDCW. Metallized teflon: 41 pF +2%, 250 VDCW.
C4206L	19A700131P35	Metallized teflon: 35 pF ±2%, 250 VDCW.
C4206M	19A700131P32	Metallized teflon: 32 pF +2%, 250 VDCW.
C4206H	19A700131P28	Metallized teflon: 28 pF ±2%, 250 VDCW.
C4207*	19A134666P1	Silver mica: 18 pF +5%, 500 VDCW; sim to Electro
C4208	19A116192P1	Motive Type DM154CR. Deleted by REV C. Ceramic: 0.01 uF ±20%, 50 VDCW; sim to Erie 8121 Special.
C4209LL	19A700131P41	Metallized teflon: 41 pF +2%, 250 VDCW.
C4209L	19A700131P37	Metallized teflon: 37 pF ±2%, 250 VDCW.
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Marche M	MBOL GE I	PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
March Marc	C4209M 19A70	700131P35	Metallized teflon: 35 pF ±2%, 250 VDCW.	C4224H*	19A134666P1		С4240Н	19A700131P28	Metallized teflon: 28 pF ±2%, 250 VDCW.			
March Marc	C4209H 19A70	700131P32	Metallized teflon: 32 pF ±2%, 250 VDCW.	C422511	194700131039	1	C4241LL*	19A134666P3				(Part of printed board 19C321425G1).
Column C						<u>-</u>	C4241L*	19A134666P1	i			
Martin					19A700131P32					and	19B226708G1	Jumper.
				C4225H	19A700131P28	Metallized teflon: 28 pF ±2%, 250 VDCW.	C4241M*	19A134666P1		i	104130479D2	Stran
	į		-	C4226LL	19A700131P41	Metallized teflon: 41 pF ±2%, 250 VDCW.	C4241H*	19A134666P1		W4211	19813047972	Strap.
	1		Motive Type DM154CR. Deleted by REV C.	C4226L	19A700131P35	Metallized teflon: 35 pF ±2%, 250 VDCW.	C4242LL	19A116656P4J0	· · · · · · · · · · · · · · · · · · ·		į	FREQUENCY SELECTING NETWORKS
10.00 10.0	C4211L* 19A13	134666P1	Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C.	1		<u> </u>			0 PPM.	Z4201LL	19A134666P3	freq, 500 VDCW; simm to Dilectron
State Stat	C4211M* 19A13	134666P1	Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro			<u>-</u> '					101194CCCP1	
	C4211H* 19A13	134666P1	•	C4227*	19813466671		thru	194116655P20		Z4201L	19413466621	freq, 500 VDCW; sim to Dilectron
Secondary Company Co				C4228	19A116192P1			19A116655P18	Ceramic disc: 680 pF +10%, 1000 VDCW; sim to RMC	74201M	19A134666P1	Frequency Network: selective, 470-630 MHz res.
State Stat	C4212LL 19A11	116656P4J0		C4229LL	19A700131P41				Type JF Discap.	J.201		freq, 500 VDCW; sim to Dilectron
Column Section Secti	C4212L 19A13	134100P19	Ceramic disc: 1 pF ±0.1 pF, temp coef 0 ±250 PPM	C4229L	19A700131P37	Metallized teflon: 37 pF ±2%, 250 VDCW.	C4247	19A116655P20		Z4201H	19A134666P1	Frequency Network: selective, 470-630 MHz res.
Column C	C4214 19A70	701413P32	Mica: 82 pF ±5%, 100 VDCW.	C4229M	19A700131P35	Metallized teflon: 35 pF ±2%, 250 VDCW.		19A116655P18				freq, 500 VDCw; sim to Directron TC501:NPO:240J:SLAC.
1.00 1.00	C4214LL 19A13	134666P3		C4229H	19A700131P32	Metallized teflon: 32 pF ±2%, 250 VDCW.			Type or Discap.	Z4202	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron
Second Column Second Colum	C4214L* 19A13	134666P1	Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro	C4230LL	19A700131P43	_	C4265L	19A116656P3J0				TC501:NPO:240J:SLAC.
Windows Window	I	l	Motive Type DM154CR. Deleted by REV C.			· - ′		19A134100P20		Z4203LL	19A134666P3	Prequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron
Authorities Control	U4214M▼ 19A13	134006P1				· - ·			±120 PPM.		10110466554	
Ministry	C4214H* 19A13	134666P1		1		_	C4266L	19A116656P3J0		Z4203L	19A134666P1	freq, 500 VDCW; sim to Dilectron
1907 1907	C4215LL 19A70	700131P39		C42316E	194134000F3		C4266M	19A134100P20		Z4203M	19A134666P1	Frequency network: selective, 470-630 MHz res.
Authors Auth	C4215L 19A70	700131P35	Metallized teflon: 35 pF ±2%, 250 VDCW.	C4231L*	19A134666P1		and					freq, 500 VDCW; sim to Dilectron
Authorities	C4215M 19A70	700131P32	Metallized teflon: 32 pF ±2%, 250 VDCW.	C4231M*	19A134666P1	Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro	C4268*	19B209723P4	Tantalum: 6.8 uF ±20%, 35 VDCW. Added by REV B	Z4203H	19A134666P1	Frequency network: selective, 470-630 MHz res.
## Authority Security Securit	C4215H 19A70	700131P28	Metallized teflon: 28 pF ±2%, 250 VDCW.	04001774	1011046667				MEDMINAL S			
## (2000)13192 Malliand etfine: 30 pf 250, 30 TOC. CASSAL Malliand etfine: 20 pf 250, 30 TOC. CASSAL Malliand	C4216LL 19A70	700131P41	Metallized teflon: 41 pF ±2%, 250 VDCW.	C4231H*	19413466671		E4201	194134263P1		Z4204LL	19A134666P3	Frequency network: selective, 400-500 MHz res.
1311-10031799 1311-10031799 1311-10031799 1311-10031799 1311-10031799 1311-10031799 1311-10031791 1311-1003179		1	_	C4232LL	19A116656P4J0	Ceramic disc: 4 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	2.201		229-1082-00-0-590.			TC501:NPO:330J:SLAC.
10.11.00.00.00.00.00.00.00.00.00.00.00.0	1	1		C4232L	19A134100P19	Ceramic disc: 1 pF ±0.1 pF, temp coef 0 ±250 PPM	G4211	19A134263P1		Z4204L	19A134666P1	freq, 500 VDCW; sim to Dilectron
Active Process Acti		1	-	C4234LL*	19A134666P3				ANDHOMODO		1011010000	1
1001159971 Special Correction O.01 of 1205, 50 YOCK, and to Dirice \$121 Special Correction Special Corre	1081	13400011		C42241 *	10413466601		1 4202	19413044762		Z4204M	19413466671	freq, 500 VDCW; sim to Dilectron
19470013191 Metallized teflos: 37 PF 255, 300 VOCV. C023344 Intelliged teflos: 37 PF 255, 300 VOCV. C023344 Intelliged teflos: 38 PF 255, 300 VOCV. Intelliged teflos: 38 PF 255, 300 VOCV. C023344 Intelliged t	C4218 19A11	116192P1		C4234L*	19413400071	Motive Type DM154CR. Deleted by REV C.				7.4204H	19A134666P1	Frequency network: selective, 470-630 MHz res.
Modeling 18 Aprolishes	C4219LL 19A70	700131P41	Metallized teflon: 41 pF ±2%, 250 VDCW.	C4234M*	19A134666P1							freq, 500 VDCW; sim to Dilectron
184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. C4230L 184700131785 Metallized teflon: 35 pf 25, 200 VDCV. Metallized teflon: 35	C4219L 19A7	700131P37	Metallized teflon: 37 pF ±2%, 250 VDCW.	C4234H*	19A134666P1		L4206	19A701091G1	Coil.	Z4205	19A134666P1	Frequency network: selective, 470-630 MHz res.
### Markelined refine: 32 of 724, 200 VCV. ### VC4200L 19A700131P35 ### Wetallized refine: 32 of 724, 200 VCV. ### VC4200L 19A700131P35 ### Wetallized refine: 35 of 725, 200 VCV. ### VC4200L 19A700131P35 ### Wetallized refine: 35 of 725, 200 VCV. ### Wetallized refine: 36 of 725	C4219M 19A70	700131P35	Metallized teflon: 35 pF ±2%, 250 VDCW.	C422511	104700131030		L4208	19A130447G2	Coil.			
184700131793 Metallized teflor: 43 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N 184700131793 Metallized teflor: 32 Pf 25, 200 VDCV. C4235N Metallize	C4219H 19A7	700131P32	Metallized teflon: 32 pF ±2%, 250 VDCW.			_	L4209	19A701091G1	Coil.	Z4206LL	19A134666P3	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron
194700131935 Metallized teflon: 35 pf 23K, 250 VDCW. Metallized teflon: 37 pf 23K, 250 VDCW. Metallized te			•			·	L4211	19A130447G1	Coil.			TC501:NPO:330J:SLAC.
194700131P28 Metallized teflon: 28 pf 25, 250 VDCW. 194700131P32 Metallized teflon: 32 pf 25, 250 VDCW. 194700131P32 Metallized te			_ ,			·	L4212	19A701091G1	Coil.	Z4206L	19A134666P1	freq, 500 VDCW; sim to Dilectron
### 184134666P3 194134666P3 19413466P3 1941	1		· · ·	C4236LL	19A700131P41	Metallized teflon: 41 pF ±2%, 250 VDCW.			RESISTORS		1011010000	
Motive Type DMIS4CR. Deleted by REV C. C4238H 19A13466691 Silver mica: 18 pf ±55, 500 VDCW; sim to Electro Motive Type DMIS4CR. Deleted by REV C. C4238H 19A700131928 Metallized teflon: 32 pf ±28, 250 VDCW. Metallized teflon: 32 pf ±28, 250 VDCW. Silver mica: 18 pf ±55, 500 VDCW; sim to Electro Motive Type DMIS4CR. Deleted by REV C. C4238H 19A700131928 C4237* 19A13466691 Silver mica: 18 pf ±55, 500 VDCW; sim to Electro Motive Type DMIS4CR. Deleted by REV C. C4238H 19A700131928 C4238H 19A7001319			Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro	C4236L	19A700131P35	Metallized teflon: 35 pF ±2%, 250 VDCW.	R4201	19A700111P39	Composition: 100 ohms ±5%, 2 w.	Z4206M	19A134666P1	freq, 500 VDCW; sim to Dilectron
19413466691 Silver mica: 18 pf 25, 500 VDCW; sim to Electro Motive Type DMIS4CR. Deleted by REV C.			Motive Type DM154CR. Deleted by REV C.	-		Metallized teflon: 32 pF ±2%, 250 VDCW.	and	19A700112P39	Composition: 100 ohms ±5%, 1 w.	Z4206H	19A134666P1	Frequency network: selective, 470-630 MHz res.
19A134666P1	C4221L* 19A1	134666P1	Silver mica: 18 pF +5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C.	į		· · ·	R4203					freq, 500 VDCW; sim to Dilectron
19A134666P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A22LL 19A134066P1 Silver mica: 27 pp ±5%, 500 VDCW; sim to Electro Active Type DM154CR. Deleted by REV C. 19A22LL 19A134666P1 Silver mica: 27 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A22LL 19A134666P1 Silver mica: 27 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A22LL 19A134666P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A22LL 19A134666P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A234666P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A234666P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A234666P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A234666P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A234666P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A234666P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A234666P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A234666P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A234666P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A234666P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A234666P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A234666P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A23466P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A23466P1 Silver mica: 18 pp ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted	C4221M* 19A1	134666P1	Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro	C4237*	19A134666P1	Silver mica: 18 pF +5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C.	thru	19A700113P15	Composition: 10 ohms ±5%, 1/2 w.	Z4207LI	19A134666P3	Frequency network: selective, 400-500 MHz res.
Motive Type DMI54CR. Deleted by REV C. Ceramic disc: 4 pf ±0.5 pf, 500 VDCW, temp coef of PM. Ceramic disc: 1 pf ±0.1 pf, temp coef of ±250 PPM Ceramic disc	C4221H* 19A1	134666P1	Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro	C4238	19A116192P1		ı	194700111239	Composition: 100 ohms +5%. 2 w-			TC501:NPO:330J:SLAC.
C4222L 19A134666P1			Motive Type DM154CR. Deleted by REV C.	C4239LL	19A700131P41		and	157.55111155	<u>-</u>	Z4207L	19A134666P1	
19A134666P3 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 2420H 19A134666P1 Frequency network: selective, 470-630 MHz re freq, 500 VDCW; sim to Dilectron TC501:NPO:2407:SLAC. 19A134666P1 Frequency network: selective, 470-630 MHz re freq, 500 VDCW; sim to Dilectron TC501:NPO:2407:SLAC. 2420H 19A134666P1 Frequency network: selective, 470-630 MHz re freq, 500 VDCW; sim to Dilectron TC501:NPO:3407:SLAC. 2420H 19A134666P1 Frequency network: selective, 470-630 MHz re freq, 500 VDCW; sim to Dilectron TC501:NPO:3407:SLAC. 2420H 19A134666P1 Frequency network: selective, 470-630 MHz re freq, 500 VDCW; sim to Dilectron TC501:NPO:3407:SLAC.	C4222LL 19A1	116656P4J0				_						TC501:NPO:240J:SLAC.
19A134666P3 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 27 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 2	C4222L 19A1	134100P19	Ceramic disc: 1 pF ±0.1 pF, temp coef 0 ±250 PPM	C4239M	19A700131P35	Metallized teflon: 35 pF ±2%, 250 VDCW.	2,515	1	T	Z4207M	19A134666P1	freq, 500 VDCW; sim to Dilectron
19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro Motive Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro C4240L 19A700131P37 Metallized teflon: 37 pF ±2%, 250 VDCW. 19A134666P1 Table Type DM154CR. Deleted by REV C. 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro C4240L 19A700131P35 Metallized teflon: 35 pF ±2%, 250 VDCW. 19A134666P1 Table Type DM154CR. Deleted by REV C. 24208 19A134666P1 Frequency network: selective, 470-630 MHz re freq, 500 VDCW; sim to Dilectron TC501:PO: 240JL 19A134666P1 Table Type DM154CR. Deleted by REV C. 24208 19A134666P1 Frequency network: selective, 470-630 MHz re freq, 500 VDCW; sim to Dilectron TC501:PO: 240JL 19A134666P1 Table Type DM154CR. Deleted by REV C.	C4224LL 19A1	134666P3		C4239H	19A700131P32	Metallized teflon: 32 pF ±2%, 250 VDCW.	R4210	19A700111P39	Composition: 100 ohms ±5%, 2 w.		10412466671	
Motive Type DM154CR. Deleted by REV C. C4240L 19A700131P37 Metallized teflon: 37 pF ±2%, 250 VDCW. T4201 thru c4224M* 19A134666P1 Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro C4240M 19A700131P35 Metallized teflon: 35 pF ±2%, 250 VDCW. T4208 19A134666P1 Frequency network: selective, 470-630 MHz refreq, 500 VDCW; sim to Dilectron	24224L* 19A1	134666P1	Silver mica: 18 pF ±5%, 500 VDCW; sim to Electro	C4240LL	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.		[TRANSFORMERS	Z4207H	19813406611	freg. 500 VDCW; sim to Dilectron
24224M* 19A134666P1 Silver mica: 18 pr +5%, 500 VDCW; sim to Electro C4240M 19A700131P35 Metallized teflon: 35 pr +2%, 250 VDCW. T4208 freq, 500 VDCW; sim to Dilectron			Motive Type DM154CR. Deleted by REV C.			- - ·	thru	19A130446G1	Coil.	Z4208	19A134666P1	Frequency network: selective, 470-630 MHz res.
	C4224M* 19A1	134666P1		C4240M	19A700131P35	Metallized teflon: 35 pF ±2%, 250 VDCW.						freq, 500 VDCW; sim to Dilectron

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SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
Z4209LL	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron			
Z4209L	19A134666P1	TC501:NPO:330J:SLAC. Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	K201	19A700061P1	Hermetic sealed: 180 to 341 ohms coil res, 8-16.3 VDC; sim to GE 3SAV1760A2, CP Clare HFW-1201558, or Potter-Brumfield HCM6160.
Z4209M	19A134666P1	TC501:NPO:240J:SLAC. Frequency network: selective, 470-630 MHz res.			
Z4209H	19A134666P1	freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Frequency network: selective, 470-630 MHz res.	W4280 thru W4283		(Part of printed board 19D424367P1).
		freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC.			LOW PASS FILTER MODULE 19C321424G4 (Deleted from 19D424888 by REV A)
Z4210LL	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC.			
Z4210L	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:2400:SLAC.	C4280H C4281H	19A700131P9 19A700131P18	Metallized teflon: 9 pF + or 0.5 pF, 250 VDCW. Metallized teflon: 18 pF + 0.5 pF, 250 VDCW.
Z4210M	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:2403:SLAC.	C4282H	19A700131P12	Metallized teflon: 12 pF ±0.5 pS, 250 VDCW. Teflon/Mica: 220 pF ±5%, 250 VDCW.
Z4210H	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	С4283Н	194700015P37	
Z4211	19A134666P1	TC501:NPO:240J:SLAC. Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	L4281 and L4282	19B226709G1	Jumper.
Z4212LL	19A134666P3	TC501:NPO:240J:SLAC. Frequency network: selective, 400-500 MHz res.	D-1202		JACKS AND RECEPTACLES
		freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC.	J202 and J203	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim NTTF-1058.
Z4212L	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC.	J206 and		(Part of K201).
Z4212M	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:2400:SLAC.	J207 J208	4033513P4	Contact, electrical: sim to Bead Chain L93-3.
Z4212H	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:2403:SLAC.			
Z4213* thru Z4216*	19A143581G1	Network assembly. Added to G5 by REV M. Added to G9 by REV E.	K201	19A116722P1	Hermetic sealed: 125 ohms ±20%, 1 form C contact, 9.6 to 15.8 VDC (over the temperature range indicated). (Includes J206 & J207).
		LOW PASS FILTER 19C327024G3 420-450 MHz (LL) 19C327024G4 450-512 MHz (H) (Added to 19D424888 by REV A)	W4280 thru W4283		
C4290LL	19A700014P4				HEAT SINK 19B219688G7 ("M" SERIES) 19B219688G19 ("E" SERIES)
C4290EL	19A700131P9	Metallized teflon: 9 pF ±0.5 pF, 250 VDCW.			
C4291LL.	19A700131P20	Metallized teflon: 20 pF ±0.5 pF, 250 VDCW.	C297	19A116708P1	Ceramic, feed-thru: 0.01 uF +100-0%; sim to E
C4291H	19A700131P18	Metallized teflon: 18 pF ±0.5 pF, 250 VDCW.	and C298		Style 327050X-5W0103P.
C4292LL	19A700131P13	Metallized teflon: 13 pF ±0.5 pF, 250 VDCW.	C299	19A115680P10	Electrolytic: 200 uF +150-10%, 18 VDCW; sim t
C4292H	19A700131P12	Metallized teflon: 12 pF ±0.5 pF, 250 VDCW.			Mallory Type TTX.
C4293	19A700015P37	Teflon/Mica: 220 pF ±5%, 250 VDCW.			DIODES AND RECTIFIERS
			CR295	19A116783P1	Silicon.
L4291LL	19B226709G2	Jumper. (Includes L4292LL).			MISCELLANEOUS
L4291H	19B226709G1	Jumper. (Includes L4292H).		5492178P2	Washer, spring tension: sim to Wallace Barnes
L4292LL		(Part of L4291LL).		19A702182P1	375-20. (Used with Q202). Spacer. (Used with Q202).
L4292H		(Part of L4291H).	İ	19A702782P5	Nut, hex, brass: No. 8-32. (Used with Q202)
		JACKS AND RECEPTACLES		N44P9010C6	Machine screw: No. 4-40 x 5/8. (Used with Q
J202 and	19A700049P2	Connector, receptacle: 500 VDCW maximum; sim to		19A700068P1	Insulator, bushing. (Used with Q215).
J203				19A116023P1	Insulator, plate. (Used with Q215).
J206 and J207	19A134263P2	Contact, electrical: sim to Selectro 229-1071.		19B201074P312	Tap screw, Phillips POZIDRIV®: No. 6-32 x 3/4 (Secures Filter Assembly).
J208	4033513P4	Contact, electrical: sim to Bead Chain L93-3.		19B201074P306	Tap screw, Phillips POZIDRIVe: No. 6-32 x 3/8 (Secures Filter Board & jumper between 100 War Module & Filter Board).
				19C321442P1	Insulator. (Located under 100 Watt Module).
	1		1	i	

SYMBOL	GE PART NO.	DESCRIPTION
	19C321441P1	Insulator. (Located under 40 Watt Module).
	19A701332P4	Insulator, washer: nylon. (Used with Q201).
	N80P9006C6	Machine screw, phillips: No. 4-40 x 3/8. (Secures Q215).
	7141225P2	Hex nut: No. 4-40. (Secures Q215).
	N402P35C6	Lockwasher, steel: No. 4. (Secures Q215).
	N80P13010C6	Machine screw, phillips head: No. 6-32 x 5/8 (Secures 40 Watt Module).
	19A129434P1	Washer, fiber. (Located on terminals of C297 8 C298).
	19D416732G7	Heat sink. ("M" SERIES).
	19D417105G7	Heat sink. ("E" SERIES).
	19A129639P1	Cover. (Located on "E" SERIES Heat Sink).
	19B201074P305	Tap screw, Phillips POZIDRIV®: No. 6-32 x 5/16 (Secures 19A129639P1 cover).

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Hevision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

- REV. A PA Assembly 19D424888G14-17 & G31-34 To incorporate new low-pass filter. Deleted 19C321424. Added 19C327024.
- REV. A 40 Watt Module 19C321347G5-8
- To improve power output at cold temperatures. Added CR204 & CR205.
- REV. B 40. Watt Module 19C321347G5-8
 - Torimprove operation.
 In 19C32134765: deleted C213 and changed C252LLB.
 In 19C32134766: deleted C253M and added C252LB.
 In 19C32134768: deleted C257M and added C252MB.
 In 19C32134768: deleted C233H, C257H and added C252
- REV. C 40 Watt Module 19C321347G5-8
- To improve operation. Deleted C209 and R203. Changed R204.
- REV. D 40 Watt Module 19C321347G5
- To improve operation. Added C209 and R203. REV. E - 40 Watt Module 19C321347G5
- To improve station operation. Added C213.
- REV. D 40 Watt Module 19C321347G6-8 To improve operation. Changed C206.
- REV. F 40 Watt Module 19C321347G5
- To improve operation. Changed C206.
- REV. E 40 Watt Module 19C321347G7 & G8
 - To improve RF Output: In 19C321347G7, 8: Changed C238. In 19C321347G8 : Changed C237.
- REV. E 40 Watt Module 19C321347G6 REV. F 40 Watt Module 19C321347G7, 8 REV. G 40 Watt Module 19C321347G5
- - To improve operation. Changed C207L & C207M. Deleted C208L, C208M and C208H. Changed C209LL designation to C209. Added R203 to groups 6, 7 and 8.
- REV. H 40 Watt Module 19C321347G5
 - To increase output at 406 MHz. Changed C252LLB. Deleted C239. Added C239LLB.
- REV. A 100 Watt Module 19D423006G5-8
 - To improve performance. Changed R4208 and R4209.
- REV. B To improve stability. Added C4268.
- REV. F 40 Watt Module 19C321347G6
 - To improve stability if PA impedance mismatch occurs. Added R216 and C262.
- REV. G To improve operation. Deleted C262.

- REV. H 40 Watt Module 19C321347G6
 REV. K 40 Watt Module 19C321347G5
 REV. G 40 Watt Module 19C321347G7,
 REV. J 40 Watt Module 19C321347G5
 REV. A 40 Watt Module 19C321347G9
- To correct Parts List. Added C240LL.
- REV. B 40 Watt Module 19C321347G9
 - To improve stability. Changed Q203LL.
- REV. C 40 Watt Module 19C321347G9 To improve operation of Power Control Circuit when used as driver for 100 Watt PA. Added C263 and C264.
- REV. J 40 Watt Module 19C321347G6
- To improve power output at low end of 450-470 MHz range. Changed C219.

- REV. L 40 Watt Module 19C321347G5 REV. K 40 Watt Module 19C321347G6 REV. H 40 Watt Module 19C321347G7 REV. H 40 Watt Module 19C321347G8 REV. D 40 Watt Module 19C321347G9
 - To incorporate new nomenclature for frequency selection networks.
- REV. M 40 Watt Module 19C321347G5 REV. E 40 Watt Module 19C321347G9

To improve Power output. Deleted C213LL, L207 & L210LL. Changed C257LL, C252LLB (Group 5 only), and Q203LLB. Added Z213 and Z214.

REV. N - 40 Watt Module 19C321347G5 REV. F - 40 Watt Module 19C321347G9

To improve Power output. Changed C230LL, C235LL, C236LL & C257LL. Added C213LL.

REV. C - 100 Watt Module 19D423006G5-8

To improve operation. Changed C2.

REV. D - 19D423006G5-8

To improve operation. Deleted L4201, L4204, L4207 and L4210. Added Z4213 - Z4216.

REV. B - PA Assembly 19D424888G14-G17, G31-G34

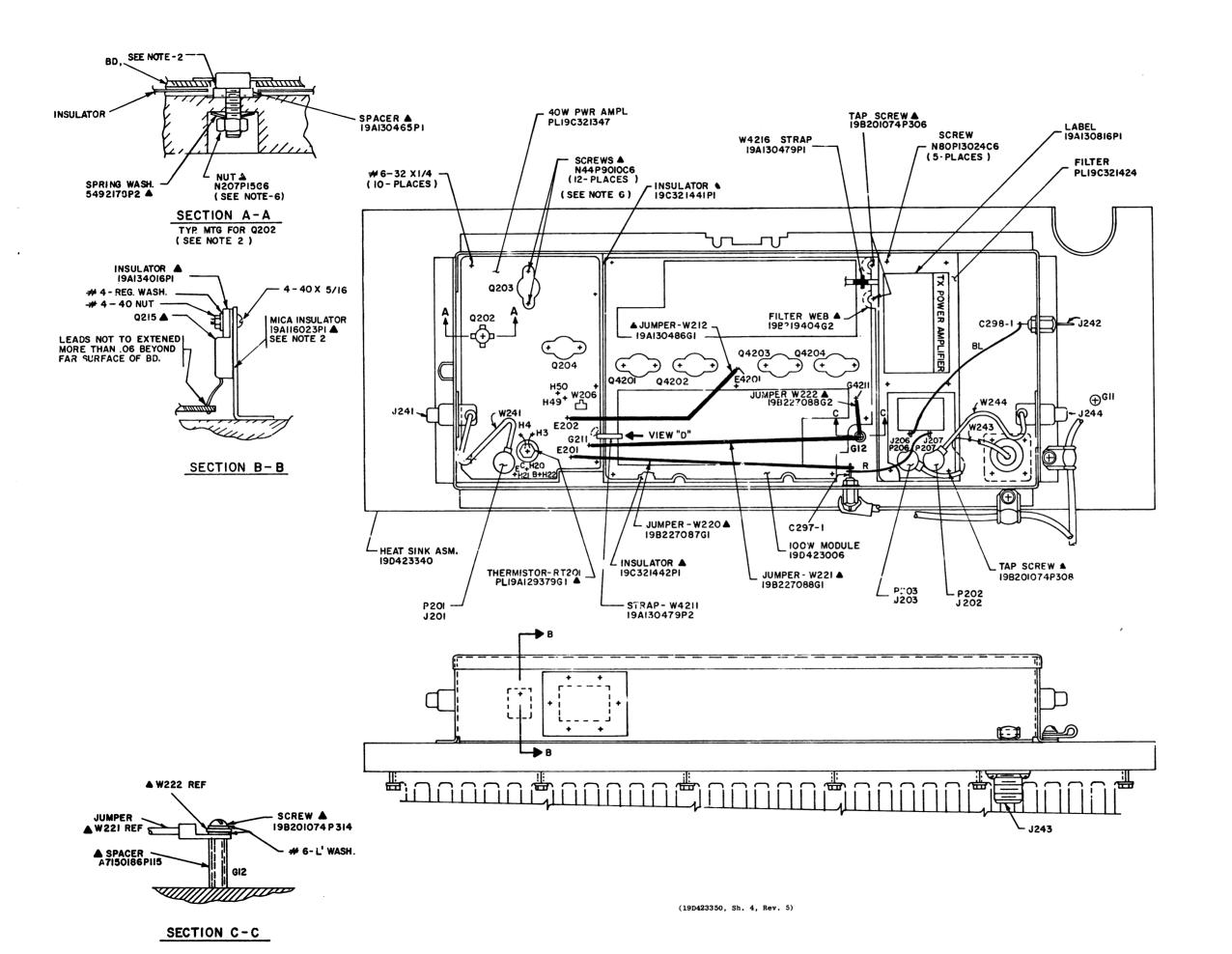
To improve operation in hot environments and to eliminate potential shots. Changed printed wire board.

REV. L - 40-Watt PA Module 19C321347G6

To increase output power. Changed C252LB and C237. Deleted R216 and C230L. R216 Was: 19A700113P15, Composition: 10 ohms ±5%, 1/2 W. C230L Was: 19A116656P4J0, Ceramic disc: 4 pf, ±0.5 pf, 500 VDCW, temp coef 0 PPM.

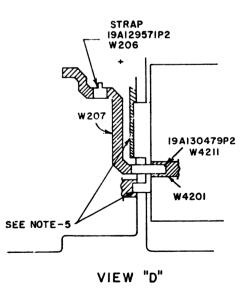
REV. M - To improve output power over 450-470 MHz range. Deleted C219L. Changed C252LB. Added C219. C219L Was: 19A116656P24J0, Ceramic disc 24 pf, ±5%, 500 VDCW, temp coef 0 PPM. C252LB Was: 19A116656P3J0, Ceramic disc: 3 pf, ±0.5 pf, 500 VDCW, temp coef 0 PPM.

REV. A - TX PA FILTER 19D424888G14, 31
To improve operation. Changed C4290LL



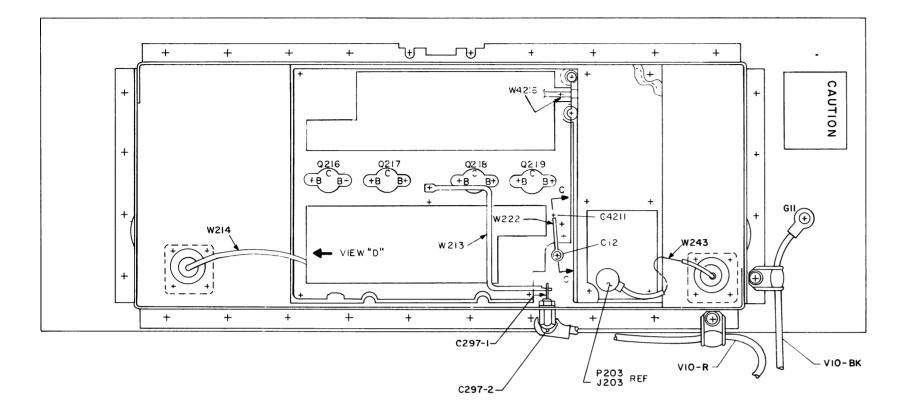
NOTES:

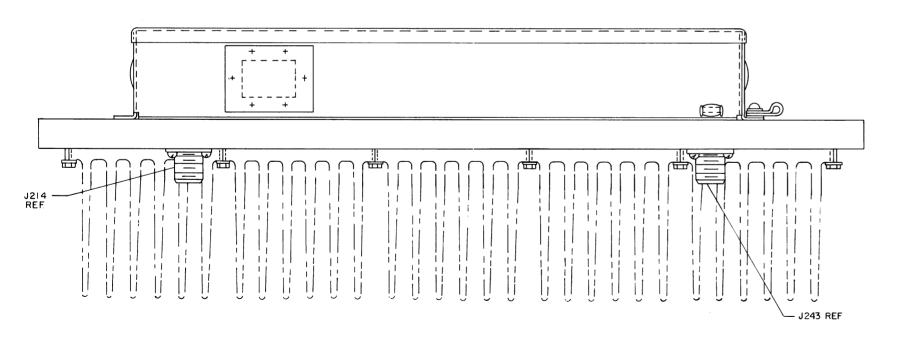
- +) 1. ▲ PART OF KIT 19A130484.
- 2 APPLY SILICONE GREASE TO BOTH SURFACES OF TRANSISTOR INSULATOR (19A116023P1), BETWEEN BOTH MTG SURFACES OF SPACER (19A130465P1) & BETWEEN MTG. SURFACE OF RT201 Q203, Q204, Q4201, Q4202, Q4203, Q4204 & HEAT SINK PER CPD PROCESS P6A-EAIII. CARE MUST BE USED SO THAT NO GREASE IS APPLIED TO THE THREADED PORTION OF THE MTG. STUD OF Q202.
- 3. SOLDER ALL ELECTRICAL CONNECTIONS.
- SOLDER STRAP TO GROUND ON 40 WATT "GCELE (190321347) AS SHOWN IN VIEW D.
- 6. TIGHTEN TRANSISTOR MTG. HANDWARE TO WITHIN 8 \pm 1 IN. LBS. FOR $_88$ HARDWARE & 6 \pm 1 IN LBS FOR $_84$ HARDWARE.
- RECOMMENDED INSTALLATION PROCEDURE OF 40 WATT MODULE (PL19C321347) IS: ASSEMBLE ALL HARDWARE LCOSE, THEN "ORQUE Q203 AND Q204 THEN TIGHTEN MOUNTING HARDWARE.
- RECOMMENDED INSTALLATION PROCEDURE OF 100 WATT MUDULE. (PL190423006) IS ASSEMBLE ALL HARDWARE LOUSE, THEN TORQUE Q4201, Q4202, Q4203, AND Q4204, THEN TIGHTEN MOUNTING HARDWARE.
- 9. SEE INTERCONNECTION DIAG. 19R622188.



OUTLINE DIAGRAM

100 WATT UHF CONTINUOUS DUTY STATION POWER AMPLIFIER





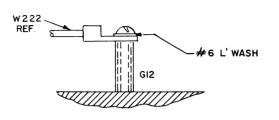
OUTLINE DIAGRAM

19D424895G40-G43 POWER AMPLIFIER USED FOR COMBINING

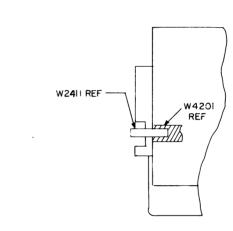
(19D433142, Rev. 0)

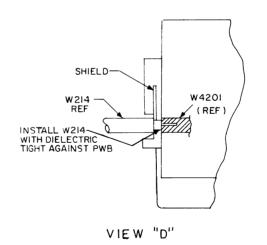


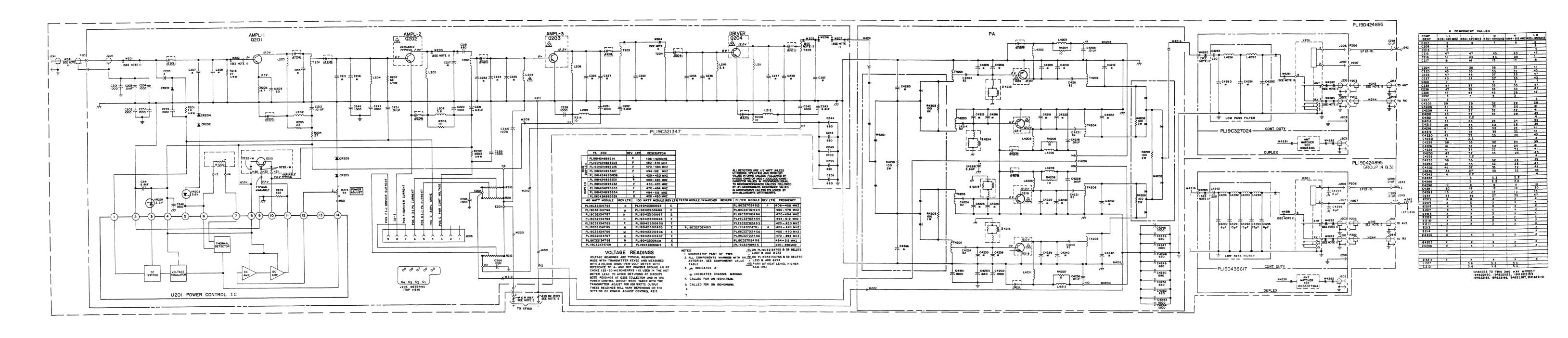
Issue 2



SECTION C-C
ROTATED APPROX. 90° CCW



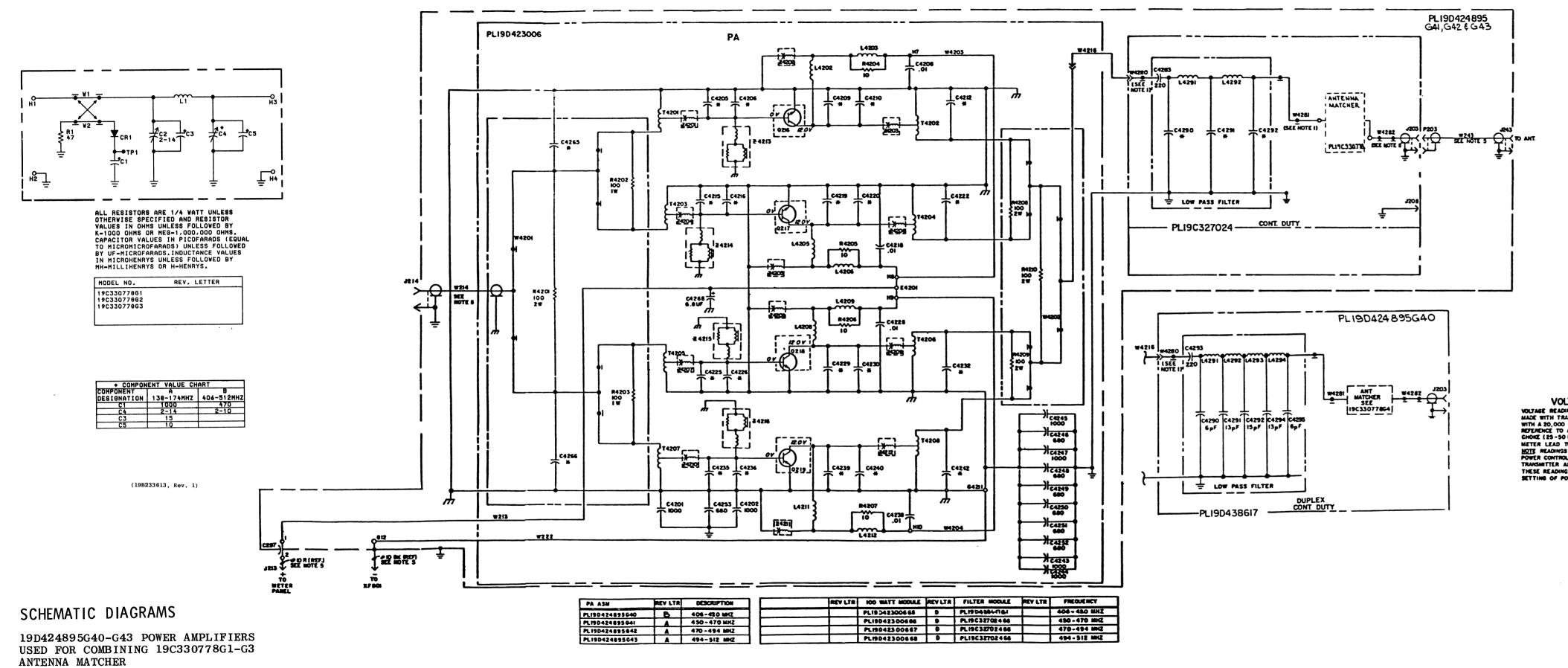




(19R622188, Rev. 43)

SCHEMATIC DIAGRAM

100 WATT UHF CONTINUOUS DUTY STATION POWER AMPLIFIER



(19R601694, Sh. 1, Rev. 3)

CHANGES TO THIS DWG MAY AFFECT 19R622150, 19R622152, 19R622153 19R622165, 19R622166, 19R622157, 19R62216 19R622164

ALL RESISTORS ARE 1/2 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY K-1000 OHMS OR MEG = 1,000,000 OHMS -CAPACITOR VALUES IN PROFARADS (EQUAL TO MICROMICROFARADS) UNLESS FOLLOWED BY UF . MICROFARADS, INDUCTANCE VALUES IN MICROHENRYS UNLESS FOLLOWED BY MH+ MILLHENRYS OR H+HENRYS

VOLTAGE READINGS VOLTAGE READINGS ARE TYPICAL READINGS

MADE WITH TRAINSMITTER KEYED AND SEASURED WITH A 20,000 ONMS-PER-VOLT METER WITH REFERENCE TO A- AND NOT CHASSIS GROUND AN RF CHOKE (25-50 MICROHENRYS) IS USED IN THE HOT METER LEAD TO AVOID DETUNING RF CIRCUITS NOTE READINGS AT 0202 COLLECTOR AND IN THE POWER CONTROL CIRCUIT WERE TAKEN WITH THE TRANSMITTER ADJUST FOR 100 WATTS OUTPUT THESE READINGS WILL VARY DEPENDING ON THE SETTING OF POWER ADJUST CONTROL REIS

L MICROSTRIP PART OF PWB. 2. ALL COMPONENTS MARKED WITH (H) ASTERISK, SEE COMPONENT VALUE

1 / MOICATES A- . + INDICATES CHASSIS GROUND

5 CALLED FOR ON 190424895

PARTS LIST

SYMBOL GE PART NO.

C204

19A116192P1

19A116655P20

19**A**116656P3J0 19A116656P8J0

19A116656P9J0

9A116656P7JO

19A116656P6J0

19A116656P8J0 L9A116656P33J0

19A116192P1

19A116656P5J0 19A700131P47

19A700131P47

9A700131P43

19A700131P43

19A700131P51

9A700131P43

19A700131P43

19A116679P18D

19A116679P16D

19A116679P15D

19A116679P13D

19A116655P18

19A116655P20

19A701534P16

19A116655P20

19A700131P41

19A700131P35

19A700131P35

19A700131P32 19A700131P43

19A700131P35

9A700131P33

9A700131P32

19A700131P47

9A700131P43

9A700131P37

DESCRIPTION

eramic: 0.01 uF + or -20%, 50 VDCW; sim to

Ceramic disc: 1000 pF + or - 10%, 1000 VDCW; sim to RMC Type JF Discap.

eramic disc: 3 pF + or -0.5 pF, 500 VDCW, temp sef 0 PPM.

Ceramic disc: 8 pF + or -0.5 pF, 500 VDCW: temp

eramic disc: 9 pF + or -0.5 pF, 500 VDCW, temp

Ceramic disc: 6 pF + or -0.5 pF, 500 VDCW, temp coef 0 PPM. (Used in G8).

Ceramic disc: 33 pF + or -5%, 500 VDCW, temp

Ceramic: 0.01 uF + or -20%, 50 VDCW; sim to Erie 8121 Special.

etallized teflon: 47 pF + or -2%, 250 VDCW.

Metallized teflon: 47 pF + or -2%, 250 VDCW. (Used in G6).

detallized teflon: 43 pF + or -2%, 250 VDCW.

Metallized teflon: 51 pF + or -2%, 250 VDCW, temp coef -130 PPM (Used in G5 and G9).

tallized teflon: 43 pF + or -2%, 250 VDCW.

Metallized teflon: 43 pF + or -2%, 250 VDCW.

Metallized teflon: 39 pF + or -2%, 250 VDCW.

Metallized teflon: 18 pF + or -0.5 pF, 250 VDCW. (Used in G5 and G9).

Metallized teflon: 16 pF + or -0.5 pF, 250 VDCW. (Used in G6).

Metallized teflon: 13 pF + or -0.5 pF, 250 VDCW. (Used in G8).

Tantalum: 6.8 uF + or -20%, 35 VDCW.

Ceramic disc: 1000 pF + or - 10%, 1000 VDCW; sim to RMC Type JF Discap.

Metallized teflon: 41 pF + or -2%, 250 VDCW, temp coef 0 -130 PPM. (Used in G5 and G9).

Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used

Peflon/mica: 35 pF + or -2%, 250 VDCW. (Used in

etallized teflon: 32 pF + or -2%, 250 VDCW. Used in G8).

fetallized teflon: 43 pF + or -2%, 250 VDCW.
[Used in G5 and G9].

Metallized teflon: 33 pF + or -2%, 250 VDCW.

letallized teflon: 32 pF + or -2%, 250 VDCW.

Metallized teflon: 47 pF + or -2%, 250 VDCW. (Used in G5 and G9).

Metallized teflon: 43 pF + or -2%, 250 VDCW.

Metallized teflon: 37 pF + or -2%, 250 VDCW. (Used in G7).

Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used in

Ceramic disc: 680 pF + or -10%, 1000 VDCW; sim to RMC Type JF Discap.

Ceramic disc: 7 pF + or - 0.5 pF, 500 VDCW, temp coef 0 PPM. (Used in G7).

oef 0 PPM. (Used in G6).

LBI-30531L
406-512 MHZ 100 WATT STATION POWER AMPLIFIER
19D424895G14-17 (CONTINUOUS DUTY) - REV C
19D424895G318 (CONTINUOUS DUTY-DUPLEX) - REV F
19D424895G39 (CONTINUOUS DUTY-DUPLEX) - REV D
19D424895G40-43 (CONTINUOUS DUTY-FOR COMBINING)

MBOL	GE PART NO.	DESCRIPTION
C297 and	19A116708P1	
C298		amps; sim to Erie 32/050X5W0103P.
C300	19A116708P1	Ceramic: 0.01 uF -0 +100%, 500 VDCW, rated 20 amps; sim to Erie 327050X5W0103P.
J213		Connector. Includes:
	19B701869P1	Connector.
	19B701869P2	Connector.
J214		Part of W214.
J243		Part of W243.
P206 and P207	4036634P1	Contact, electrical; sim to AMP 42428-2.
Q202	19A134164P2	Silicon NDN sin to Tune OMEOAS
Q202 Q203LLB	198134164P2	Silicon, NPN; sim to Type 2N5945. Silicon, NPN.
Q203LLB Q203LB	19A134239P1	Silicon, NPN. Silicon, NPN.
Q203MB	19A134239P1	Silicon, NPN.
2203НВ	19A134239P1	Silicon, NPN.
2204LL	19A134242P3	Silicon, NPN.
Q204L	19A134242P3	Silicon, NPN.
Q204H	19A134242P4	Silicon, NPN; 50 Watt.
2215	19A116753P1	Silicon, NPN.
2216 thru 2219	19A134171P2	Silicon, NPN; 35 Watt.
2217		
RT201	19A129379G1	Thermistor: 40K ohms + or - 20%, color code white; sim to Carborundum Type M0806J-5.
1212	19A130486G1	Jumper.
1213	19A143696P1	Jumper.
1214	19A129312G13	Cable.
1220	19B227087G1	Jumper: 6 inches long.
1221	19B227088G1	Jumper.
1222	19B227088G2	Jumper.
1243	19A129312G6	Cable.
1244	5491689P104	Cable, RF: approx 4 inches long, 350 VRMS, 500 VDC operating voltage.
1245	19A705906G1	Cable.
14216	19A701006P1	Strap.
		40 WATT MODULE
		19C321347G5 406-420 MHz (LL) 19C321347G6 450-470 MHz (L) - REV L
		19032134706 470-494 MHz (L) - REV L 19032134708 494-512 MHz (H) 19032134708 494-512 MHz (LL)
201	19A116655P20	Ceramic disc: 1000 pF + or - 10%, 1000 VDCW;
nd 202		sim to RMC Type JF Discap.

SYMBOL	GE PART NO.	
С226Н	19A700131P35	Teflor
C227LL	19A700131P43	Metall (Used
C227L	19A700131P37	Metall (Used
C227M	19A700131P37	Metall
С227Н	19A700131P35	(Used Teflor G8).
C228	19A116655P20	Cerami
C230LL	19A116656P7J0	sim to
C230M	19A116656P4J0	temp o
С230Н	19A116656P3J0	coef C
C231	19A116655P20	coef C
C232	19A701534P16	sim to
C235LL	19A700131P47	Metall (Used
C235L	19A700131P37	Metall (Used
C235M	19A700131P35	Teflor
С235Н	19A700131P33	Metall (Used
C236LL	19A700131P47	Metall (Used
C236L	19A700131P35	Teflor
C236M	19A700131P33	Metall (Used
C236H	19A700131P33	Metall (Used
C237LL	19A700131P47	Metall (Used
C237L	19A700131P39	Metall (Used
C237M	19A700131P37	Metall (Used
С237Н	19A700131P35	Teflon
C238LL	19A700131P47	Metall (Used
C238L	19A700131P43	Metall (Used
C238M	19A700131P43	Metall (Used
C238H	19A700131P39	Metall (Used
C241	19A134202P15	Tantal
C242	19A116655P20	Cerami sim to
C243	19A134202P15	Tantal
C244 and C245	19A116655P18	Cerami to RMC
C246 thru C250	19A116655P20	Cerami sim to
C251	19A116192P1	Cerami Erie 8
C252LLB	19A116656P5J0	Cerami
C252LB	19 A 116656P7J0	Cerami temp c
C252MB	19A116656P4J0	Cerami
С252НВ	19A116656P3J0	Cerami
	l	1

SYMBOL	GE PART NO.	DESCRIPTION	SYI	MBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.
С226Н	19A700131P35	Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used in G8).	l a	255 nd	19A116655P18	Ceramic disc: 680 pF + or -10%, 1000 VDCW; sim to RMC Type JF Discap.	R207	19A700106P35
C227LL	19A700131P43	Metallized teflon: 43 pF + or -2%, 250 VDCW. (Used in G5 and G9).		256 257LL	19A116656P5J0	,	R208	19A700113P15
C227L	19A700131P37	Metallized teflon: 37 pF + or -2%, 250 VDCW.	Н			Ceramic disc: 5 pF + or -0.5 pF, 500 VDCW, temp coef 0 PPM. (Used in G5 and G9).	R209 R210	19A700113P57 19C850605P1
C227M	19A700131P37	(Used in G6). Metallized teflon: 37 pF + or -2%, 250 VDCW.	"	260	19A116655P20	Ceramic disc: 1000 pF + or - 10%, 1000 VDCW; sim to RMC Type JF Discap.	thru R212	
С227Н	19A700131P35	(Used in G7). Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used in	l ar	263 nd 264	19A116655P20	Ceramic disc: 1000 pF + or - 10%, 1000 VDCW; sim to RMC Type JF Discap.	R213	19A116559P102
1		G8).	"	204			R214	19A700113P15
C228	19A116655P20	Ceramic disc: 1000 pF + or - 10%, 1000 VDCW; sim to RMC Type JF Discap.		R201	19A116052P1	Silicon, hot carrier: Fwd drop .350 volts max.	R215	19A700106P25
C230LL	19A116656P7J0	Ceramic disc: 7 pF + or - 0.5 pF, 500 VDCW, temp coef 0 PPM. (Used in G5 and G9).	CI	R202	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.		
C230M	19A116656P4J0	Ceramic disc: 4 pF + or -0.5 pF, 500 VDCW, temp coef 0 PPM. (Used in G7).		hru R205			thru T205	19A130446G1
С230Н	19A116656P3J0	Ceramic disc: 3 pF + or -0.5 pF, 500 VDCW, temp coef 0 PPM. (Used in G8).						
C231	19A116655P20	Ceramic disc: 1000 pF + or - 10%, 1000 VDCW; sim to RMC Type JF Discap.	l ar	201 nd 202	19A134263P1	Contact, electrical.	U201	19D423127G1
C232	19A701534P16	Tantalum: 6.8 uF + or -20%, 35 VDCW.	11	211	19A134263P1	Contact, electrical.		
C235LL	19A700131P47	Metallized teflon: 47 pF + or -2%, 250 VDCW. (Used in G5 and G9).					VR201	4036887P1
C235L	19A700131P37	Metallized teflon: 37 pF + or -2%, 250 VDCW.	J J2	201	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim to	VR202	4036887P5
C235M	19A700131P35	(Used in G6). Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used in	J J2	205	19B219374G1	NTTF-1058. Connector: 9 contacts.		
С235Н	19A700131P33	G7). Metallized teflon: 33 pF + or -2%, 250 VDCW.	L2	202	19A701091G1	Coil.	W206	19A701093P1
		(Used in G8).	11	203	19A129774P1	Coil.	W209 W210	19B226733G1 19B226734G1
C236LL	19A700131P47	Metallized teflon: 47 pF + or -2%, 250 VDCW. (Used in G5 and G9).	11	204	19A701091G1 19B219457P6	Coil.		
C236L	19A700131P35	Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used in G6).	11	206	19A700000P120	Coil, RF: 5.6 uH + or -10%; sim to Jeffers	Z201	19A134666P1
C236M	19A700131P33	Metallized teflon: 33 pF + or -2%, 250 VDCW. (Used in G7).	L2	207	19A700000P20	4422-1K. Coil, RF: 5.6 uH + or -10%; sim to Jeffers		
С236Н	19A700131P33	Metallized teflon: 33 pF + or -2%, 250 VDCW. (Used in G8).	1 ,,	208LL	19B219457P6	4421-4K. (Used in G6,G7 and G8). Coil. (Used in G5 and G9).	Z203LL	19A134666P3
C237LL	19A700131P47	Metallized teflon: 47 pF + or -2%, 250 VDCW.	1	208L	19A130650P1	Coil. (Used in G6).	Z203L	19A134666P1
C237L	19A700131P39	(Used in G5 and G9). Metallized teflon: 39 pF + or -2%, 250 VDCW.	11	208M	19A130650P1	Coil. (Used in G7).		
C237M	19A700131P37	(Used in G6). Metallized teflon: 37 pF + or -2%, 250 VDCW.	11	208H 209	19A130650P1 19A701091G1	Coil. (Used in G8). Coil.	Z203M	19A134666P1
С237Н	102700121225	(Used in G7).	11	210L	19A700000P20	Coil, RF: 5.6 uH + or -10%; sim to Jeffers	Z203H	19A134666P1
	19A700131P35	Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used in G8).	L2	210M	19A700000P20	4421-4K. (Used in G6). Coil, RF: 5.6 uH + or -10%; sim to Jeffers		
C238LL	19A700131P47	Metallized teflon: 47 pF + or -2%, 250 VDCW. (Used in G5 and G9).		210H	19A700000P20	4421-4K. (Used in G7). Coil, RF: 5.6 uH + or -10%; sim to Jeffers	Z204LL	19A134666P3
C238L	19A700131P43	Metallized teflon: 43 pF + or -2%, 250 VDCW. (Used in G6).	11			4421-4K. (Used in G8).	Z204L	19A134666P1
C238M	19A700131P43	Metallized teflon: 43 pF + or -2%, 250 VDCW. (Used in G7).	11	211	19B219457P6 19A701091G1	Coil.		
С238Н	19A700131P39	Metallized teflon: 39 pF + or -2%, 250 VDCW. (Used in G8).					Z204M	19A134666P1
C241	19A134202P15	Tantalum: 6.8 uF + or -20%, 35 VDCW.	Q2	201	19A134237P1	Silicon, NPN.	Z204H	19A134666P1
C242	19A116655P20	Ceramic disc: 1000 pF + or - 10%, 1000 VDCW; sim to RMC Type JF Discap.	Q2	202	19A134164P2	Silicon, NPN; sim to Type 2N5945.		
C243	19A134202P15	Tantalum: 6.8 uF + or -20%, 35 VDCW.	11 -	203LLB	19A134239P3	Silicon, NPN. (Used in G5 and G9).	Z205LL	19A134666P3
C244 and	19A116655P18	Ceramic disc: 680 pF + or -10%, 1000 VDCW; sim to RMC Type JF Discap.	11	203LB 203MB	19A134239P1 19A134239P1	Silicon, NPN. (Used in G6). Silicon, NPN. (Used in G7).	Z205L	19A134666P1
C245	19A116655P20	Ceramic disc: 1000 pF + or - 10%, 1000 VDCW;	Q2	203НВ	19A134239P1	Silicon, NPN. (Used in G8).		
thru C250		sim to RMC Type JF Discap.		204LL	19A134242P3	Silicon, NPN. (Used in G5 and G9).	Z205M	19A134666P1
C251	19A116192P1	Ceramic: 0.01 uF + or -20%, 50 VDCW; sim to Erie 8121 Special.	11	204L 204H	19A134242P3 19A134242P4	Silicon, NPN. (Used in G6). Silicon, NPN; 50 Watt. (Used in G7 and G8).	Z205H	19A134666P1
C252LLB	19A116656P5J0	Ceramic disc: 5 pF + or -0.5 pF, 500 VDCW, temp coef 0 PPM. (Used in G5).						
C252LB	19 A 116656P7J0	Ceramic disc: 7 pF + or - 0.5 pF, 500 VDCW,	R2	201	19A700106P63	Composition: 1K ohms + or - 5%, 1/4 w.	Z206	19A134666P1
С252МВ	19A116656P4J0	temp coef 0 PPM. (Used in G6). Ceramic disc: 4 pF + or -0.5 pF, 500 VDCW, temp	11	202	3R152P304J	Composition: 300K ohms + or -5%, 1/4 w.	Z207LL	19A134666P3
С252НВ	19A116656P3J0	coef 0 PPM. (Used in G7). Ceramic disc: 3 pF + or -0.5 pF, 500 VDCW, temp	11	203	19A700113P7 19A700113P25	Composition: 4.7 ohms + or - 5%, 1/2 w.	220,00	17.1134000F3
		coef 0 PPM. (Used in G8).	I I	205	19A700113P25	Composition: 27 ohms + or - 5%, 1/2 w. Composition: 22 ohms + or - 5%, 1/4 w.	Z207L	19A134666P1
C253	19A116655P20	Ceramic disc: 1000 pF + or - 10%, 1000 VDCW; sim to RMC Type JF Discap.	R2	206	19A700113P15	Composition: 10 ohms + or - 5%, 1/2 w.		

Power Control.

DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
Composition: 68 ohms + or - 5%, 1/4 w. Composition: 10 ohms + or - 5%, 1/2 w.	Z207M	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TCS01:NPO:2401:SLAC. (Used in G7).
Composition: 560 ohms + or - 5%, 1/2 w. Shunt resistor.	Z207H	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. (Used in G8).
Variable cermet: 5000 ohms + or - 20%, 1/2 w;	Z208LL	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. (Used in G5 and G9).
sim to CTS Series 360. Composition: 10 ohms + or - 5%, 1/2 w.	Z208L	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. (Used in G6).
Composition: 27 ohms + or - 5%, 1/4 w.	Z208M	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. (Used in G7).
Coil.	Z208H	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. (Used in G8).
INTEGRATED CIRCUITS	Z209LL	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. (Used in G5 and G9).
Power Control	Z209L	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. (Used in G6).
Zener: 500 mW, 2.3 v. nominal. Zener: 500 mW, 5.4 v. nominal.	Z209M	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. (Used in G7).
	Z209H	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. (Used in G8).
Strap. Jumper.	Z210	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC.
Jumper.	2211	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. (Used in G9).
Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC.	Z211LL	19A134666P3	Frequency network: selective, 400-500 MHz res. freg, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. (Used in G5 and G8).
Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. (Used in G5 and G9).	Z211L	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. (Used in G6).
Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. (Used in G6).	Z211M	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. (Used in G7).
Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. (Used in G7).	Z211H	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. (Used in G8).
Frequency network: selective, 470-630 MHz res. freg, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. (Used in G8).	Z213 Z214	19A143581G1 19A143581G1	Network assembly. (Used in G5 and G9). Network assembly. (Used in G5 and G9).
Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. (Used in G5 and G9).			100 WATT MODULE
Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. (Used in G6).			19D423006G5 406-450 MHz (LL) 19D423006G6 450-470 MHz (L) 19D423006G7 470-494 MHz (M) 19D423006G8 494-512 MHz (H)
Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:2403:SLBC. (Used in G7).			
Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:2403:SLAC. (Used in G8).	C4201 and C4202	19A116655P20	Ceramic disc: 1000 pF + or - 10%, 1000 VDCW; sim to RMC Type JF Discap.
Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron	C4204LL C4204L	19A701413P32 19A701413P32	Mica: 82 pF + or -5%, 100 VDCW. (Used in G5). Mica: 82 pF + or -5%, 100 VDCW. (Used in G6).
TC501:NPO:330J:SLAC. (Used in G5 and G9).	C4204M	19A701413P32	Mica: 82 pF + or -5%, 100 VDCW. (Used in G6).
Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	C4204H	19A701413P32	Mica: 82 pF + or -5%, 100 VDCW. (Used in G8).
TC501:NPO:240J:SLAC. (Used in G6). Prequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	C4205LL	19A700131P39	Metallized teflon: 39 pF + or -2%, 250 VDCW. (Used in G5).
TC501:NPO:240J:SLAC. (Used in G7). Frequency network: selective, 470-630 MHz res.	C4205L	19A700131P35	Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used in G6).
freq, 500 VDCW; sim to Dilectron PC501:NPO:240J:SLAC. (Used in G8). Prequency network: selective, 470-630 MHz res.	C4205M	19A700131P32 19A700131P28	Metallized teflon: 32 pF + or -2%, 250 VDCW. (Used in G7). Metallized teflon: 28 pF + or -2%, 250 VDCW.
freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC.			(Used in G8).
Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron PC501:NPO:330J:SLAC. (Used in G5 and G9).	C4206LL C4206L	19A700131P41 19A700131P35	Metallized teflon: 41 pF + or -2%, 250 VDCW, temp coef 0 -130 PPM. (Used in G5). Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used in
Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron FC501:NPO:240J:SLAC. (Used in G6).	C4206M	19A700131P32	G6). Metallized teflon: 32 pF + or -2%, 250 VDCW. (Used in G7).

SYMBOL

C4208

C4209H

C4210H

C4211M

C4211H

C4214LL

C4214L

C4214M

C4215L

C4215H

C4216L

C4216H

C4218

C4219M

C4220M

C4220H

C4221M

C4221H

GE PART NO.

19A700131P28

19A116192P1

19A700131P32

19A700131P28

19A701413P32

19A701413P32

19A701413P32

19A701413P32

19A701413P32

19A700131P35

19A700131P28

19A700131P35

19A700131P28

19A116192P1

19A700131P35

19A700131P35

19A700131P28

19A701413P32

19A701413P32

Mica: 82 pF + or -5%, 100 VDCW. (Used in G6).

Mica: 82 pF + or -5%, 100 VDCW. (Used in G7).

Mica: 82 pF + or -5%, 100 VDCW. (Used in G8).

C4209LL 19A700131P41

C4209L 19A700131P37

C4209M 19A700131P35

C4210LL 19A700131P43

C4210L 19A700131P37

C4210M 19A700131P35

C4211LL 19A701413P32 C4211L 19A701413P32

C4212LL 19A116656P4J0

C4212L 19A134100P20

C4214H 19A701413P32

C4215LL 19A700131P39

C4215M 19A700131P32

C4216LL 19A700131P41

C4216M 19A700131P32

C4219LL 19A700131P41

C4219L 19A700131P37

C4219H 19A700131P32

C4220LL 19A700131P43

C4220L 19A700131P37

C4221LL 19A701413P32

C4221L 19A701413P32

			T
DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
Metallized teflon: 28 pF + or -2%, 250 VDCW. (Used in G8).	C4222LL	19A116656P4J0	Ceramic disc: 4 pF + or -0.5 pF, 500 VDCW, tem coef 0 PPM. (Used in G5).
Ceramic: 0.01 uF + or -20%, 50 VDCW; sim to Erie 8121 Special.	C4222L	19A134100P20	Ceramic disc: 2.2 pF + or -0.1 pF, temp coef 0 + or -120 PPM. (Used in G6).
Metallized teflon: 41 pF + or -2%, 250 VDCW, temp coef 0 -130 PPM. (Used in G5).	C4224LL	19A701413P32	Mica: 82 pF + or -5%, 100 VDCW. (Used in G5).
detallized teflon: 37 pF + or -2%, 250 VDCW.	C4224L	19A701413P32	Mica: 82 pF + or -5%, 100 VDCW. (Used in G6).
Used in G6).	C4224M C4224H	19A701413P32 19A701413P32	Mica: 82 pF + or -5%, 100 VDCW. (Used in G7).
eflon/mica: 35 pF + or -2%, 250 VDCW. (Used in 7).	C4225LL	19A700131P39	Mica: 82 pF + or -5%, 100 VDCW. (Used in G8). Metallized teflon: 39 pF + or -2%, 250 VDCW.
etallized teflon: 32 pF + or -2%, 250 VDCW. Used in G8).	C4225L	19A700131P35	(Used in G5). Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used in G6).
etallized teflon: 43 pF + or -2%, 250 VDCW. Used in G5).	C4225M	19A700131P32	Metallized teflon: 32 pF + or -2%, 250 VDCW.
etallized teflon: 37 pF + or -2%, 250 VDCW. Used in G6).	C4225H	198700131928	(Used in G7).
eflon/mica: 35 pF + or -2%, 250 VDCW. (Used in	C4225H	194/00131928	Metallized teflon: 28 pF + or -2%, 250 VDCW. (Used in G8).
etallized teflon: 28 pF + or -2%, 250 VDCW.	C4226LL	19A700131P41	Metallized teflon: 41 pF + or -2%, 250 VDCW, temp coef 0 -130 PPM. (Used in G5).
Used in G8). .ca: 82 pF + or -5%, 100 VDCW. (Used in G5).	C4226L	19A700131P35	Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used in G6).
ca: 82 pF + or -5%, 100 VDCW. (Used in G6).	C4226M	19A700131P32	Metallized teflon: 32 pF + or -2%, 250 VDCW. (Used in G7).
ca: 82 pF + or -5%, 100 VDCW. (Used in G7).	C4226H	19A700131P28	Metallized teflon: 28 pF + or -2%, 250 VDCW. (Used in G8).
ramic disc: 4 pF + or -0.5 pF, 500 VDCW, temp ef 0 PPM. (Used in G5).	C4228	19A116192P1	Ceramic: 0.01 uF + or -20%, 50 VDCW; sim to Erie 8121 Special.
ramic disc: 2.2 pF + or -0.1 pF, temp coef 0 or -120 PFM. (Used in G6).	C4229LL	19A700131P41	Metallized teflon: 41 pF + or -2%, 250 VDCW, temp coef 0 -130 PPM. (Used in G5).
ca: 82 pF + or -5%, 100 VDCW. (Used in G5).	C4229L	19A700131P37	Metallized teflon: 37 pF + or -2%, 250 VDCW.
a: 82 pF + or -5%, 100 VDCW. (Used in G6).	C4229M	19A700131P35	(Used in G6). Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used :
ca: 82 pF + or -5%, 100 VDCW. (Used in G7).	C4229H	19A700131P32	G7). Metallized teflon: 32 pF + or -2%, 250 VDCW.
tallized teflon: 39 pF + or -2%, 250 VDCW.	C4230LL	19A700131P43	(Used in G8). Metallized teflon: 43 pF + or -2%, 250 VDCW.
flon/mica: 35 pF + or -2%, 250 VDCW. (Used in).	C4230L	19A700131P37	(Used in G5). Metallized teflon: 37 pF + or -2%, 250 VDCW.
tallized teflon: 32 pF + or -2%, 250 VDCW.	C4230M	19A700131P35	(Used in G6). Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used:
sed in G7). tallized teflon: 28 pF + or -2%, 250 VDCW.	C4230H		G7).
sed in G8). tallized teflon: 41 pF + or -2%, 250 VDCW,		19A700131P28	Metallized teflon: 28 pF + or -2%, 250 VDCW. (Used in G8).
mp coef 0 -130 PPM. (Used in G5). flon/mica: 35 pF + or -2%, 250 VDCW. (Used in	C4231LL C4231L	19A701413P32 19A701413P32	Mica: 82 pF + or -5%, 100 VDCW. (Used in G5). Mica: 82 pF + or -5%, 100 VDCW. (Used in G6).
). (Used in	C4231M	19A701413P32	Mica: 82 pF + or -5%, 100 VDCW. (Used in G7).
tallized teflon: 32 pF + or -2%, 250 VDCW. sed in G7).	C4231H	19A701413P32	Mica: 82 pF + or -5%, 100 VDCW. (Used in G8).
tallized teflon: 28 pF + or -2%, 250 VDCW. sed in G8).	C4232LL	19A116656P4J0	Ceramic disc: 4 pF + or -0.5 pF, 500 VDCW, tercef 0 PPM. (Used in G5).
ramic: 0.01 uF + or -20%, 50 VDCW; sim to le 8121 Special.	C4232L	19A134100P20	Ceramic disc: 2.2 pF + or -0.1 pF, temp coef + or -120 PPM. (Used in G6).
tallized teflon: 41 pF + or -2%, 250 VDCW, mp coef 0 -130 PPM. (Used in G5).	C4234LL	19A701413P32	Mica: 82 pF + or -5%, 100 VDCW. (Used in G5).
tallized teflon: 37 pF + or -2%, 250 VDCW.	C4234L	19A701413P32	Mica: 82 pF + or -5%, 100 VDCW. (Used in G6).
sed in G6).	C4234M C4234H	19A701413P32 19A701413P32	Mica: 82 pF + or -5%, 100 VDCW. (Used in G7). Mica: 82 pF + or -5%, 100 VDCW. (Used in G8).
ilon/mica: 35 pF + or -2%, 250 VDCW. (Used in).	C4234H	19A701413P32 19A700131P39	Metallized teflon: 39 pF + or -2%, 250 VDCW.
tallized teflon: 32 pF + or -2%, 250 VDCW. sed in G8).	C4235L	19A700131P35	(Used in G5). Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used
tallized teflon: 43 pF + or -2%, 250 VDCW. sed in G5).			G6).
tallized teflon: 37 pF + or -2%, 250 VDCW. sed in G6).	C4235M	19A700131P32	Metallized teflon: 32 pF + or -2%, 250 VDCW. (Used in G7).
flon/mica: 35 pF + or -2%, 250 VDCW. (Used in).	C4235H	19A700131P28	Metallized teflon: 28 pF + or -2%, 250 VDCW. (Used in G8).
tallized teflon: 28 pF + or -2%, 250 VDCW.	C4236LL	19A700131P41	Metallized teflon: 41 pF + or -2%, 250 VDCW, temp coef 0 -130 PPM. (Used in G5).
ca: 82 pF + or -5%, 100 VDCW. (Used in G5).	C4236K	19A700131P35	Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used in G6).
den. 00 mm t au 59 100 mm (m. 1 1 mm)	C4236W	108700131932	Motallized tofler: 22 mE t am 29 250 UDGE

C4236M 19A700131P32

C4236H 19A700131P28

19A116192P1

C4238

Metallized teflon: 32 pF + or -2%, 250 VDCW.

letallized teflon: 28 pF + or -2%, 250 VDCW.
Used in G8).

Ceramic: 0.01 uF + or -20%, 50 VDCW; sim to Erie 8121 Special.

LBI30201

LBI30201

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
C4239LI	19A700131P41	Metallized teflon: 41 pF + or -2%, 250 VDCW,	R4208	19A700111P39	Composition: 100 ohms + or - 5%, 2 w.					19B201074P204	Tap screw, phillips POZIDRIV: No. 4-40 x 1/4.
C4239L	19A700131P37	temp coef 0 -130 PPM. (Used in G5). Metallized teflon: 37 pF + or -2%, 250 VDCW.	thru R4210	198/001111939	Composition: 100 omms v or - 5e, 2 w.	W4280		Part of Printed Wire Board 19D424367Pl.			(Secures W241).
1		(Used in G6).				thru W4283				19D417513G1 19B201074P306	Cover, Heat Sink Assembly. Tap screw, Phillips POZIDRIV: No. 6-32 x 3/8.
C4239M	19A700131P35	Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used in G7).	T4201 thru	19A130446G1	Coil.	W4284	19A130607G3	Cable, RF: approx .7 of an inch. (Used in G5 and G6).			(Secures Filter Board & jumper between 100 watt module and Filter Board).
C4239H	19A700131P32	Metallized teflon: 32 pF + or -2%, 250 VDCW. (Used in G8).	T4208					LOW PASS FILTER		19A134260P1 4029974P1	Insulator cover. (Used with Q215). Insulator, plate: aluminum. (Used with Q215).
C4240LI	19A700131P43	Metallized teflon: 43 pF + or -2%, 250 VDCW. (Used in G5).	ŀ					19D438617G1 406-420 MHz MATCHER 19D438617G2 406-420 MHz MOBILE		4036994P1	Terminal, solderless. (Used with Q215).
C4240L	19A700131P37	Metallized teflon: 37 pF + or -2%, 250 VDCW. (Used in G6).	W4203 and W4204	19B226708G1	Jumper.					19A115222P3	Washer, shield. (Secures Q215).
C4240M	19A700131P35	Teflon/mica: 35 pF + or -2%, 250 VDCW. (Used in G7).	W4211	19A130479P2	Strap.	C4290	19A700131P6	Metallized teflon: 6 pF + or -0.5 pF, 250 VDCW.		N210P9B6	Hex nut, steel: No. 4-40. (Secures Q215).
C4240H	19A700131P28	Metallized teflon: 28 pF + or -2%, 250 VDCW. (Used in G8).	1			C4291	19A700131P13	Metallized teflon: 13 pF + or -0.5 pF, 250 VDCW.			
C4241LL	19A701413P32	Mica: 82 pF + or -5%, 100 VDCW. (Used in G5).	Z4202	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	C4292 C4293	19A700131P15 19A700015P37	Metallized teflon: 15 pF + or -0.5 pF, 250 VDCW. Teflon/Mica: 220 pF + or -5%, 250 VDCW.			
C4241L	19A701413P32	Mica: 82 pF + or -5%, 100 VDCW. (Used in G6).	Z4205	19A134666P1	TC501:NPO:240J:SLAC. Frequency network: selective, 470-630 MHz res.	C4294	19A700131P13	Metallized teflon: 13 pF + or -0.5 pF, 250 VDCW.		-	
C4241M C4241H	19A701413P32 19A701413P32	Mica: 82 pF + or -5%, 100 VDCW. (Used in G7). Mica: 82 pF + or -5%, 100 VDCW. (Used in G8).	"""	13,123,00011	freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC.	C4295	19A700131P6	Metallized teflon: 6 pF + or -0.5 pF, 250 VDCW.			
C4242LL	ı	Ceramic disc: 4 pF + or -0.5 pF, 500 VDCW, temp	Z4208	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	C4296 and C4297	19A701624P4	Ceramic, disc: 6 pF + or -0.5 pF, 500 VDCW, temp coef 0 PPM + or -60. (Used in G2).			
C4242L	19A134100P20	coef 0 PPM. (Used in G5). Ceramic disc: 2.2 pF + or -0.1 pF, temp coef 0	Z4211	19A134666P1	TC501:NPO:240J:SLAC. Frequency network: selective, 470-630 MHz res.						
C4243	19A116655P20	+ or -120 PPM. (Used in G6). Ceramic disc: 1000 pF + or - 10%, 1000 VDCW;	27211	198134000F1	freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC.	J202	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim to			
thru C4245	134110033120	sim to RMC Type JF Discap.	Z4213 thru	19A143581G1	Network assembly.	J203	19A700049P2	NTTF-1058. (Used in G2). Connector, receptacle; 500 VDCW maximum; sim to			
C4246	19A116655P18	Ceramic disc: 680 pF + or -10%, 1000 VDCW; sim to RMC Type JF Discap.	Z4216			J206	19A134263P2	NTTF-1058. Contact, electrical: sim to Selectro 229-1071.			
C4247	19A116655P20	Ceramic disc: 1000 pF + or - 10%, 1000 VDCW; sim to RMC Type JF Discap.			LOW PASS FILTER	and J207	19813420372	(Used in G2).			
C4248	19A116655P18	Ceramic disc: 680 pF + or -10%, 1000 VDCW; sim			19C327024G3 406-450 MHz (LL) 19C327024G4 450-512 MHz (H) 19C327024G5 406-450 MHz (LL) DUPLEX	J4201 thru	19A116364P2	Contact, electrical; sim to AMP 86182-7. (Used in G1).			
thru C4253		to RMC Type JF Discap.	1	i	19C327024G6 450-512 MHz (H) DUPLEX 19C327024G9 406-450 MHz (LL) MATCHER 19C327024G10 450-512 MHz (H) MATCHER	J4204					
C4265L	19A116656P3J0	Ceramic disc: 3 pF + or -0.5 pF, 500 VDCW, temp coef 0 PPM. (Used in G6).				K201	19A700061P1	RELAYS	1		·
C4265M	19A134100P20	Ceramic disc: 2.2 pF + or -0.1 pF, temp coef 0 + or -120 PPM. (Used in G7).	C4290LL	19A700014P4	Metallized teflon: 10 pF + or - 5%, 250 VDCW.	K201	198/0006121	Hermetic sealed: 180 to 341 ohms coil res, 8-16.3 VDC; sim to GE 3SAV1760A2, CP Clare HFW-1201558, or Potter-Brumfield HCM6160. (Used			
С4265Н	19A134100P20	Ceramic disc: 2.2 pF + or -0.1 pF, temp coef 0 + or -120 PPM. (Used in G8).	С4290Н	19A700131P9	(Used in G3 and G5). Metallized teflon: 9 pF + or -0.5 pF, 250 VDCW.			in G2).			
C4266L	19A116656P3J0	Ceramic disc: 3 pF + or -0.5 pF, 500 VDCW, temp coef 0 PPM. (Used in G6).	C4291LL	19A700131P20	(Used in G4 and G6). Metallized teflon: 20 pF + or -0.5 pF, 100	L4291	ļ ·	Part of Printed Wire Board 19D438616Pl.			
C4266M	19A134100P20	Ceramic disc: 2.2 pF + or -0.1 pF, temp coef 0 + or -120 PPM. (Used in G7).	C4291H		VDCW. (Used in G3 and G5). Metallized teflon: 18 pF + or -0.5 pF, 250	thru L4294					
С4266Н	19A134100P20	Ceramic disc: 2.2 pF + or -0.1 pF, temp coef 0 + or -120 PPM. (Used in G8).			VDCW. (Used in G4 and G6).						
C4268	19A701534P16	Tantalum: 6.8 uF + or -20%, 35 VDCW.	1	19A700131P13	Metallized teflon: 13 pF + or -0.5 pF, 250 VDCW. (Used in G3 and G5).	W4280 thru		Part of Printed Wire Board.	İ		
			C4292H	19A700131P12	Metallized teflon: 12 pF + or -0.5 pF, 250 VDCW. (Used in G4 and G6).	W4282 W4283		Part of Printed Wire Board.			
E4201	19A134263P1	Contact, electrical.	C4293	19A700015P37	Teflon/Mica: 220 pF + or -5%, 250 VDCW. (Used in G3,G4,G5 and G6).	1					
G4211	19A134263P1	Contact, electrical.					19A701332P4	Insulator, washer: nylon. (Used with Q201).			
			J202	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim to NTTF-1058. (Used in G3 and G4).		19A702182P1	Spacer. (Used with Q202).			
L4202 L4203	19A130447G2 19A701091G1	Coil.	J203	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim to NTTF-1058. (Used in G3,G4,G5 and G6).		5492178P2	Washer, spring tension: sim to Wallace Barnes 375-20. (Used with Q202).			
L4205	19A130447G1	Coil.	J206	19A134263P2	Contact, electrical: sim to Selectro 229-1071.		19C321442P1	Insulator. (Located under 100 watt module).			
L4206	19A701091G1	Coil.	and J207		(Used in G3 and G4).		19C321441P1 N44P9010B6	Insulator. (Located under 40 watt module). Machine screw: No. 4-40 x 5/8. (Used with Q203).			
L4208 L4209	19A130447G2 19A701091G1	Coil.	J208	4033513P4	Contact, electrical: sim to Bead Chain L93-3. (Used in G3 and G4).		19A702782P5	Nut, hex, brass: No. 8-32. (Used with Q202).			
L4211	19A130447G1	Coil.			RELAYS		19B201074P314	Tap screw, Phillips POZIDRIV: No. 6-32 x 7/8. (Secures W221 & W222 to spacer).			
L4212	19A701091G1	Coil.	K201	19A700061P1	Hermetic sealed: 180 to 341 ohms coil res, 8-16.3 VDC; sim to GE 3SAV1760A2, CP Clare		N80P13016B6	Machine screw, panhead: No. 6-32 x l. (Secures filter assembly).			
					HFW-1201558, or Potter-Brumfield HCM6160. (Used in G3 and G4).		19B219404G1	Web filter.			
R4201	19A700111P39	Composition: 100 ohms + or - 5%, 2 w.					7139898P3	Nut, hex, brass: No. 1/4-28. (Secures C297 & C298).			
R4202 and R4203	19A700112P39	Composition: 100 ohms + or - 5%, 1 w.	L4291LL	19B226709G2	Jumper.		19B226212G1	Heat sink. (Center sections - Quantity 3).			
R4204 thru	19A700113P15	Composition: 10 ohms + or - 5%, 1/2 w.	L4291H	19B226709G1	Jumper.		19B226212G2	Heat sink. (W241 end - Quantity 1).			
R4207			L4292LL L4292H		Part of L4291LL. Part of L4291H.		19B226212G3	Heat sink. (Caution nameplate end - Quantity 1).			
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ANTENNA MATCHING UNIT 19C330778G1 HIGH BAND 19C330778G2 UHF LOW POMER 19C330778G3 UHF HIGH POMER 19C330778G4 UHF HIGH POMER 19C330778G4 UHF HIGH POMER

PARTS LIST

	SYMBOL	GE PART NO.	DESCRIPTION
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١	ClA	19A116192P1	Ceramic: 0.01 uF + or -20%, 50 VDCW; sim to Erie 8121 Special. (Used in Gl).
	C1B	19A116192P2	Ceramic: 470 pF + or -20%, 50 VDCW; sim to Erie 811-A050-W5R-471M. (Used in G2 and G3).
١	C2	19A700008P2	Variable: 2.28 to 14.13 pF; sim to EF Johnson 187-0109-005.
١	СЗА	19 A 116656P15J0	Ceramic disc: 15 pF + or -5%, 500 VDCW, temp coef 0 PPM. (Used in G1).
۱	C4A	19A700008P2	Variable: 2.28 to 14.13 pF; sim to EF Johnson 187-0109-005. (Used in G1).
١	C4B	19A700008P1	Variable: 2.04 to 9.9 pF, 250V peak. (Used in G2,G3 and G4).
l	C5A	19A116656P10J0	Ceramic disc: 10 pF + or -0.5 pF, 500 VDCW, temp coef 0 PPM. (Used in G1).
١			
	CR1	19A700047P3	Silicon: 100 mM; sim to 1N6263. (Used in Gl,G2 and G3).
١			
١	LIA	19A143343P1	Coil. (Used in Gl).
١	LIB	19A143342P1	Coil. (Used in G2,G3 and G4).
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١	1		RESISTORS
١	R1	19A700106P31	Composition: 47 ohms + or - 5%, 1/4 w. (Used in G1,G2 and G3).
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*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES REV. A - 40 Watt Module 19C32134769

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

- REV. A - PA Assembly 19D424895G40-G43
- Incorporated in initial shipment.
- REV. A-D 100 Watt Module 19D423006G5-G8 Incorporated in initial shipment.

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV. A - PA Assembly 19D424888G14-17 & G31-34

To incorporate new low-pass filter. Deleted 19C321424. Added 19C327024.

PEV. A - 40 Watt Module 19C321347G5-8 To improve power output at cold temperature. Added CR204 & CR205. REV. B - 40 Watt Module 19C321347G5-8

PRODUCTION CHANGES

To improve operation.
In 19C321347G5: deleted C213 and changed C252LLB.
In 19C321347G6: deleted C233L, C257L and added C252LB.
In 19C321347G7: deleted C257M and added C252MB.
In 19C321347G8: deleted C233H, C257H and added C252HB.

REV. C - 40 Watt Module 19C321347G5-8 To improve operation. Deleted C209 and R203. Changed R204.

REV. D - 40 Watt Module 19C321347G5 To improve operation. Added C209 and R203.

REV. E - 40 Watt Module 19C321347G5

To improve station operation. Added C213. REV. D - 40 Watt Module 19C321347G6-8

To improve operation. Changed C206.

REV. F - 40 Watt Module 19C321347G5 To improve operation. Changed C206.

REV. E - 40 Watt Module 19C321347G7, 8 To improve RF output.
In 19C321347G7, 8: Changed C238.
In 19C321347G8 : Changed C237.

REV. E - 40 Watt Module 19C321347G6

REV. F - 40 Watt Module 19C321347G7, 8 REV. G - 40 Watt Module 19C321347G5

To improve operation. Changed C207L & C207M. Deleted C208L, C208M & C208H. Changed C209LL designation to C209. Added R203 to groups 6, 7 and 8.

REV. H - 40 Watt Module 19C321347G5 To increase output at 406 MHz. Changed C252LLB. Deleted C239. Added C239LLB.

REV. A - 100 Watt Module 19D423006G5-8 To improve performance. Changed R4208 and R4209.

REV. B - To improve stability. Added C4268.

REV. F - 40 Watt Module 19C321347G6 To improve stability if PA impedance mismatch occurs. Added C262 and R216.

REV. G - To improve operation. Deleted C262.

To correct Parts List. Added C240LL.

REV. H - 40 Watt Module 19C321347G6

REV. K - 40 Watt Module 19C321347G5

REV. G - 40 Watt Module 19C321347G7, 8

REV. C - 40 Watt Module 19C321347G9

To improve operation of Power Control Circuit when used as driver for 100 Watt PA. Added C263 and C264.

REV. J - 40 Watt Module 19C321347G5 REV. B - 40 Watt Module 19C321347G9

To improve stability. Changed Q203LL. REV. A - PA Assembly 19D424895G14-17, G31-34

REV. B - To improve ground between 40 Watt and 100 Watt Module. Added interconnecting DA Jumper wire between grounds.

REV. J - 40 Watt Module 19C321347G6 To improve power output at low end of 450-470 MHz range. Changed C219.

REV. L - 40 Watt Module 19C321347G5 REV. K - 40 Watt Module 19C321347G6 REV. H - 40 Watt Module 19C321347G7 REV. H - 40 Watt Module 19C321347G8 REV. D - 40 Watt Module 19C321347G9

To incorporate new nomenclature for frequency selection networks.

REV. M - 40 Watt Module 19C321347G5 REV. E - 40 Watt Module 19C321347G9

To improve Power output. Deleted C213LL, L207 & L210LL. Changed C257LL, C252LLB (Group 5 only), and Q203LLB. Added Z213 and Z214.

REV. N - 40 Watt Module 19C321347G5 REV. F - 40 Watt Module 19C321347G9

To improve Power output. Changed C230LL, C235LL, C236LL and C257LL. Added C213LL.

REV. C - 100 Watt Module 19D423006G5-8

To improve operation. Changed C2.

REV. D - 19D423006G5-8 To improve operation. Deleted L4201, L4204, L4207 and L4210. Added Z4213 - Z4216.

REV. A - PA Assembly 19D424895G39

To incorporate new transistor. Changed Q215.

REV. B - PA Assembly 19D424895G14-17, G31-34

To improve ground between 40 Watt Module and 100 Watt Module. Added DA Jumper wire to interconnect grounds on the 40 and 100 Watt modules.

REV. C - To incorporate new transistor. Changed Q215.

REV. B - PA Assembly 19D424895G39 REV. D - PA Assembly 19D424895G31-34

To improve operation in duplex applications. Change Low Pass Filter.

REV. D - PA Assembly 19D424895G14-G17

To improve operation in hot environments. Changed printed wire board.

REV. E - PA Assembly 19D424895G14-G17

To improve operation in hot environments and to eliminate potential shorts. Changed printed wire board.

REV. L - 40 Watt Module 19C321347G6

- 40 Watt Module 19C32134766

To increase power output. Deleted C230L and R216. Changed C237 and C252LB.
C230L was: 19A116656P4J0, Ceramic disc: 4 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.
C237L was: 19A116952P47, Metallized teflon: 47 pf ±2%, 250 VDCW.
C252LB was: 19A116656P7J0, Ceramic disc: 7 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.
R216 was: 19A700113P15, 10 ohms ±5%, 1/2 W.

REV. M - To improve output power in 450-470 MHz range. Deleted C219L. M - To improve output power in 450-470 MHz range. Deleted C219L. Changed C252LB. Added C219. C219L was: 19A116656P4JO, Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef 0 PPM. C252LB was: 19A116656P3JO, Ceramic disc: 3 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.

REV G - PA Assembly 19D424895G14 & G31
To reduce spurious radiation, added C300 and W245.

REV B - PA Assembly 19D424895G40

This addendum provides revision letter changes not yet incorporated in this publication.

REV. F - 100 WATT MODULE 19D423006G8

To improve power out at high end of split. Added C4212H, C4222H, C4232H, C4242H, C4269, C4270, C4271 and C4272.

C4212H is 19A701624P1 - Ceramic, disc: 3 pF ± 0.5 pF. C4222H is 19A701624P1 - Ceramic, disc: 3 pF ± 0.5 pF. C4232H is 19A701624P1 - Ceramic, disc: 3 pF ± 0.5 pF. C4242H is 19A701624P1 - Ceramic, disc: 3 pF ± 0.5 pF. C4269H is 19A701624P1 - Ceramic, disc: 3 pF ± 0.5 pF. C4270H is 19A701624P1 - Ceramic, disc: 3 pF ± 0.5 pF. C4271H is 19A701624P1 - Ceramic, disc: 3 pF ± 0.5 pF. C4272H is 19A701624P1 - Ceramic, disc: 3 pF ± 0.5 pF.